

ENEE 359a

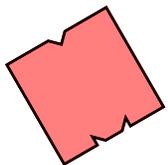
Digital VLSI Design

Some Parasitics & How to Deal with Them

Prof. Bruce Jacob
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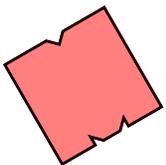
Credit where credit is due:

Slides contain original artwork (© Jacob 2004) as well as material taken liberally from Irwin & Vijay's CSE477 slides (PSU), Schmit & Strojwas's 18-322 slides (CMU), Dally's EE273 slides (Stanford), Wolf's slides for *Modern VLSI Design*, and/or Rabaey's slides (UCB).



Overview

- ***Circuit Integrity* — Project-review presentation**
- **Capacitive Parasitics**
- **Resistive Parasitics**
- **Inductive Parasitics**



ENEE 359a
Lecture/s 14+15
Parasitics

Bruce Jacob

University of
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SLIDE 3

RF and Circuit Integrity in Digital Systems

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AFOSR-MURI Annual Review, October 2004



UNIVERSITY OF MARYLAND

Overview

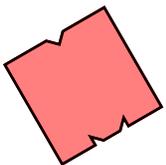
How Digital Circuits & Systems Are Built, and Some Ways in Which They Fail

- Components of Digital Systems
- RF- and Temperature-Related Vulnerabilities
 - **Data** Inputs and Networks
 - **Clock** Inputs and Networks
 - **Power/Ground** Inputs and Networks
- Circuit Design: Our Device-Under-Test

Recent Work

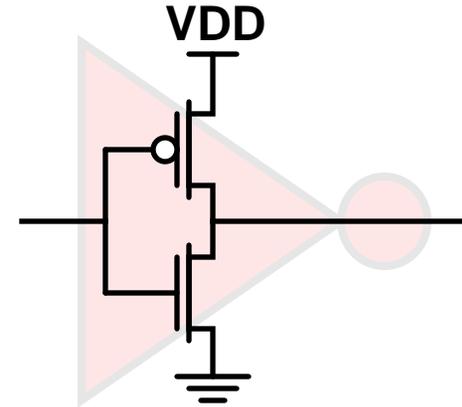
- Comparison of Vulnerability: DUT's Clock/Data Inputs
- [DUT: test chip fabricated in AMI's 0.5 μ m process]
- Custom Chip Design & Fabrication for ESD Studies

Future Work

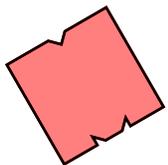
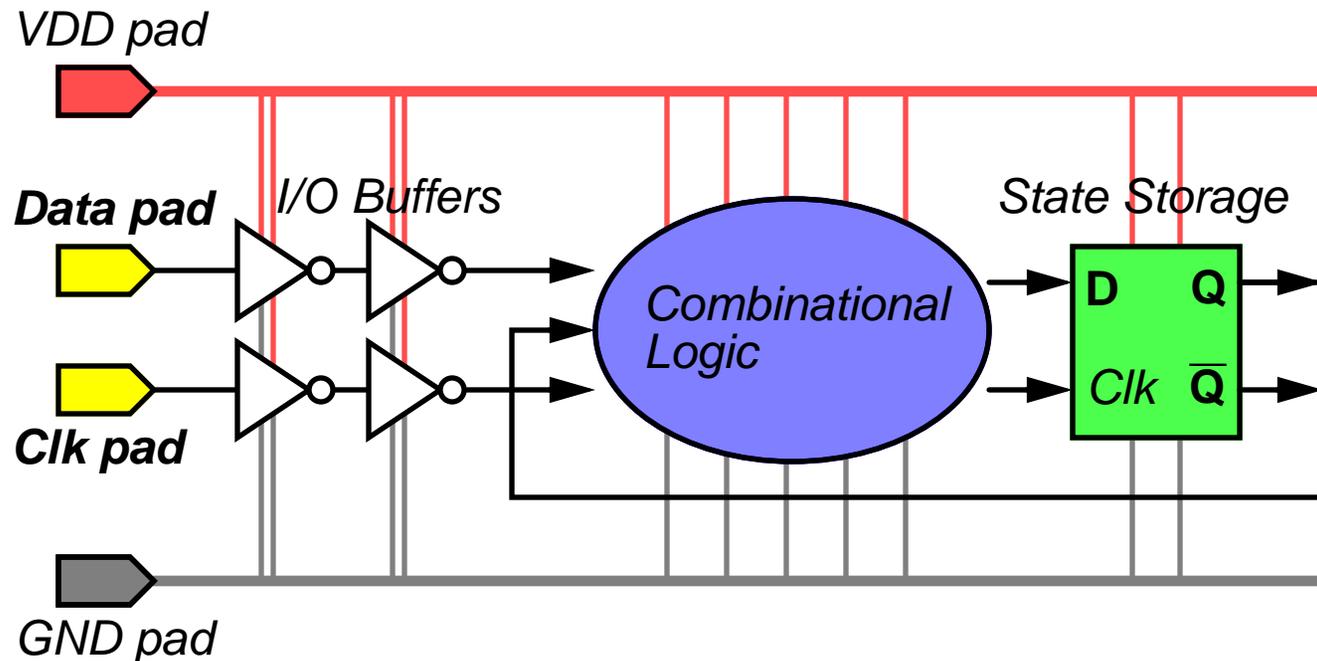


Digital Systems: A Primer

Simple Digital *Circuit*:

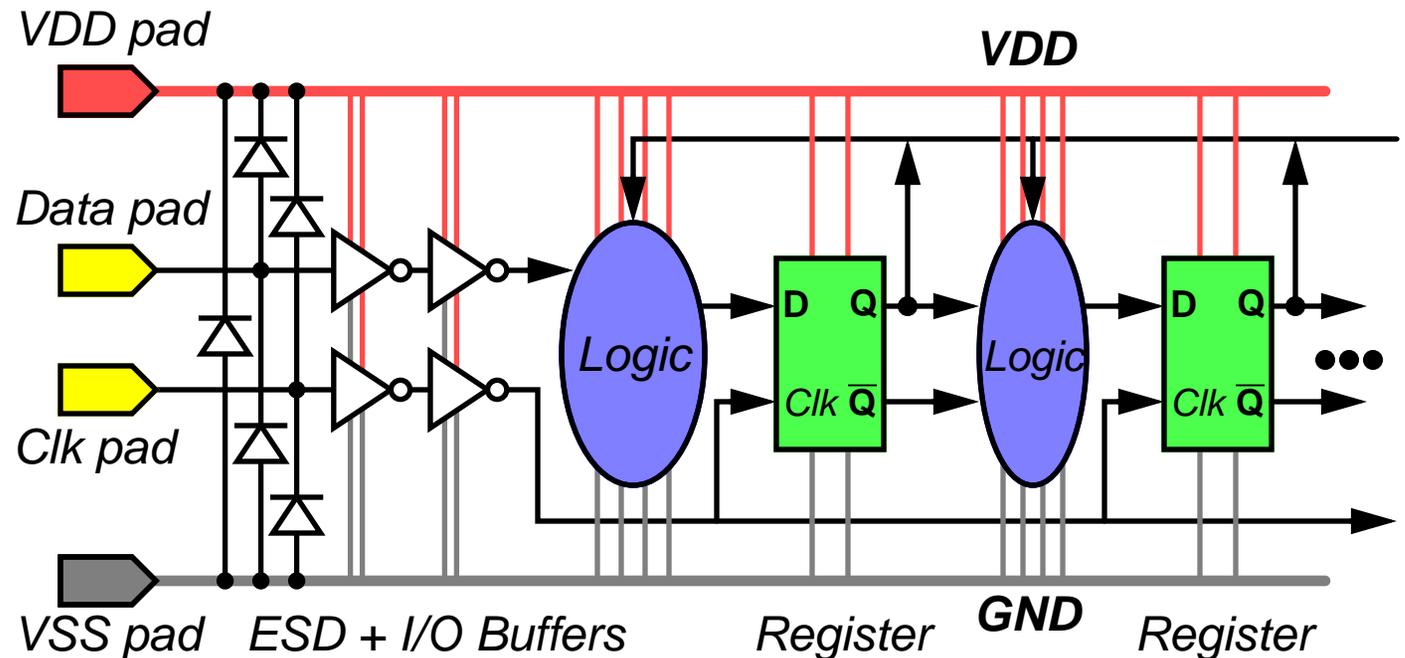


Simple Digital *System*:



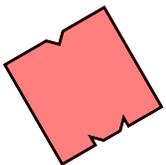
Digital Systems: A Primer

Components of Digital Systems



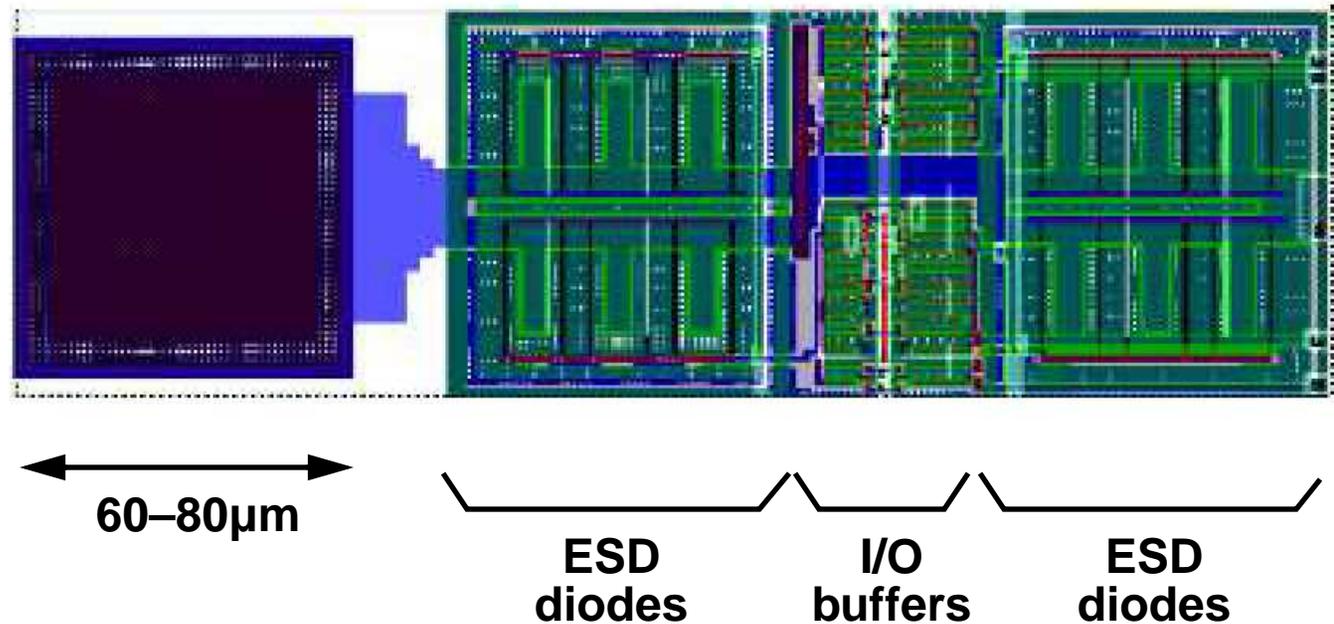
Groundplanes play significant role:

- Provide references for input amplifiers
- Allow CMOS circuits to behave as signal repeaters (with high input impedance, low output impedance)



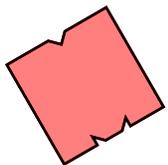
Digital Systems: A Primer

Components of Digital Systems



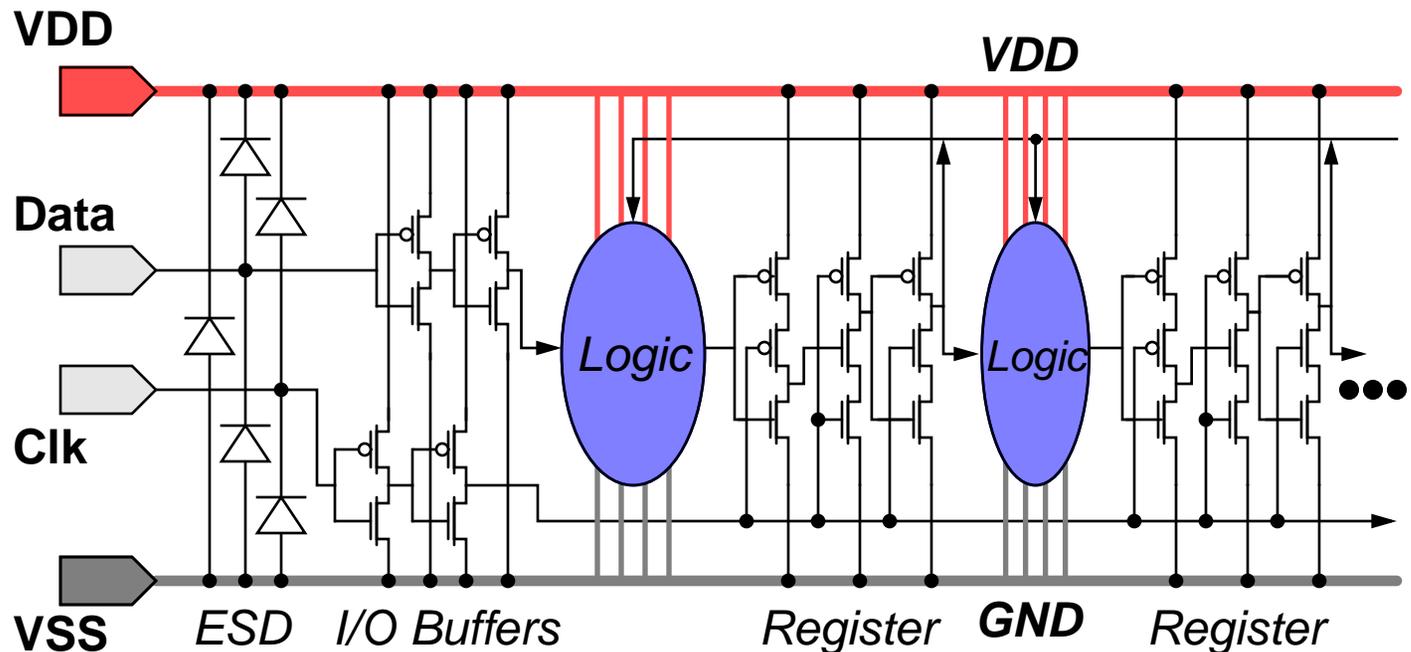
I/O Pads play significant role:

- Enormous capacitances, require enormous gates to drive them (and the pins & off-chip traces)
- Big gates => big currents; fast clocks => small dt ... VDD/VSS leads have inductance => $L di/dt$ noise



Digital Systems: A Primer

Components of Digital Systems



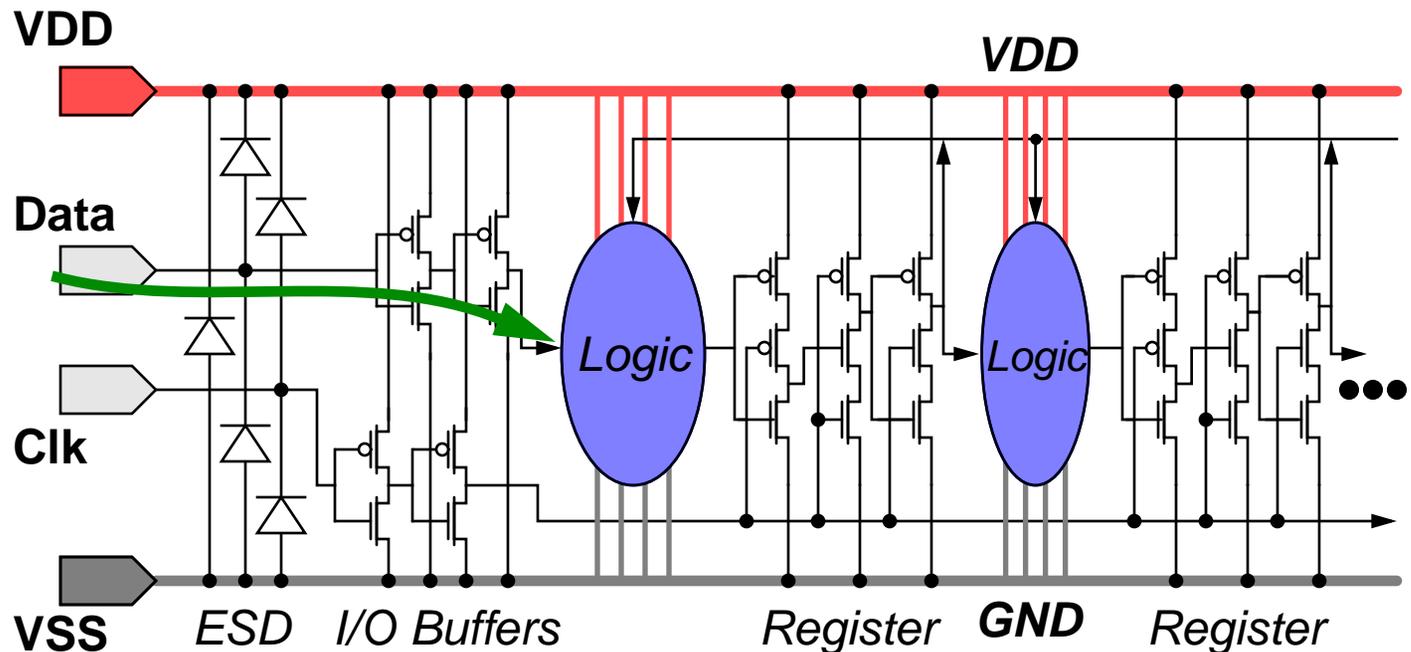
At the bottom are 'just' a bunch of MOSFETs

- Each register shown holds one bit
- Each I/O pad requires its own ESD, receivers, & drivers
- Logic blocks can be arbitrarily large/complex

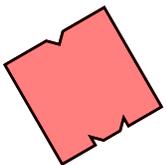


Circuit Integrity: *Data*

How To Make This System Fail ...

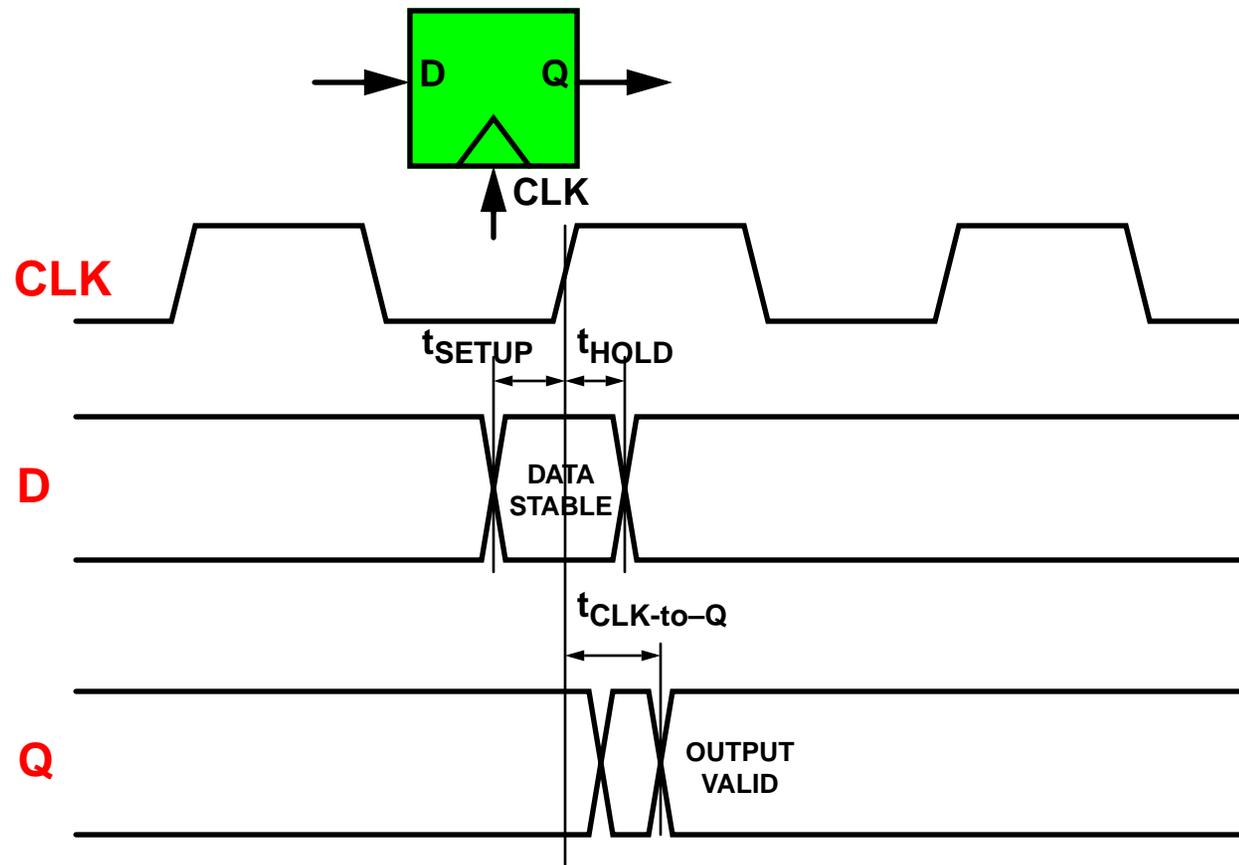


- RF that makes it this far (past initial I/O buffers) has corrupted the system: only solution is to use higher level bus- or packet-encoding techniques
- Corrupted data can lead to incorrect results, software crash/reboot, transmission to remote nodes, etc.

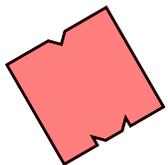


Sequential Circuits Primer

SET-UP and HOLD times

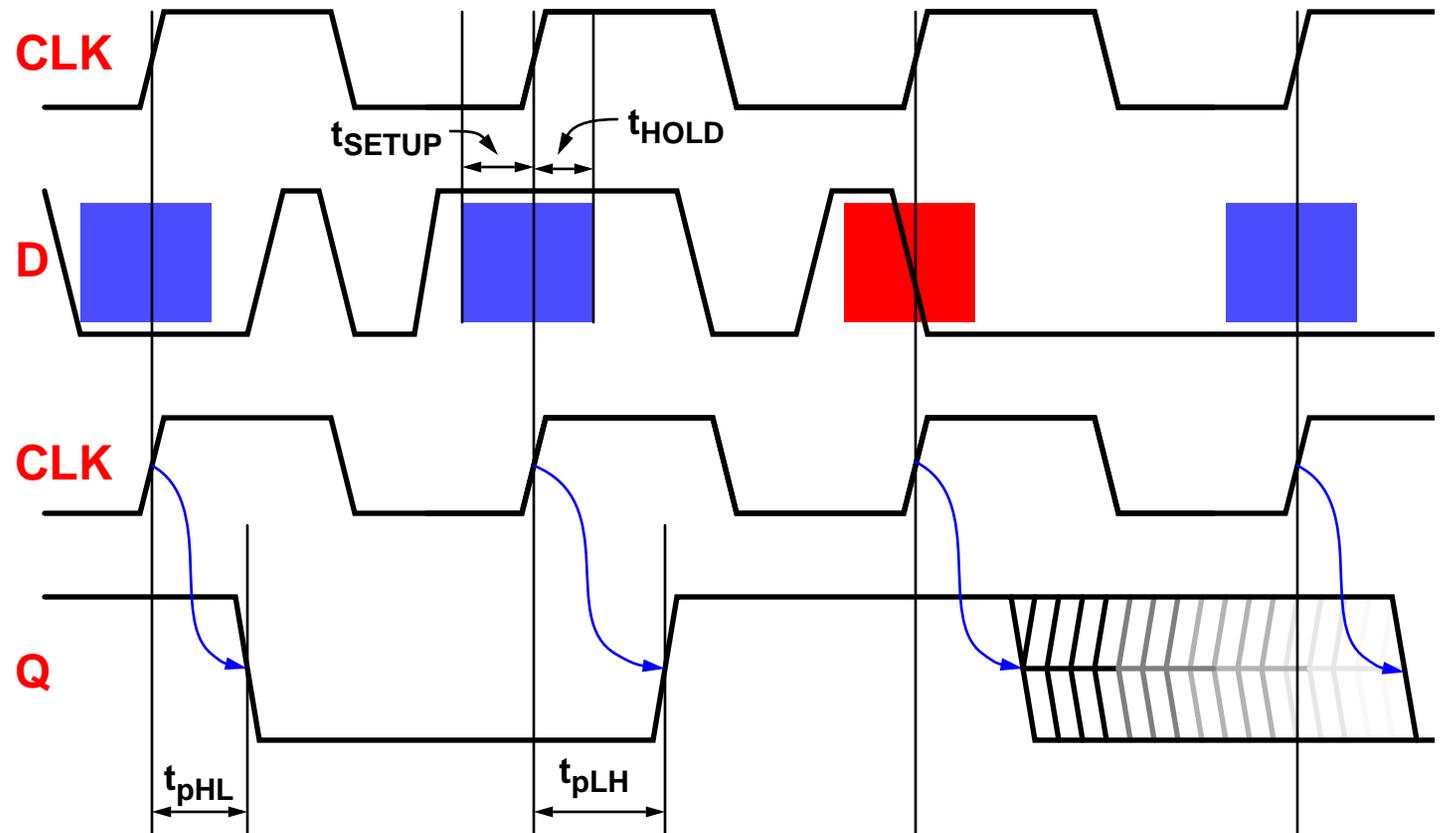


- Storage elements (latches, registers) expect data and clock edges to be timed perfectly (e.g., within 20ps)



Sequential Circuits Primer

SET-UP and HOLD time, metastability

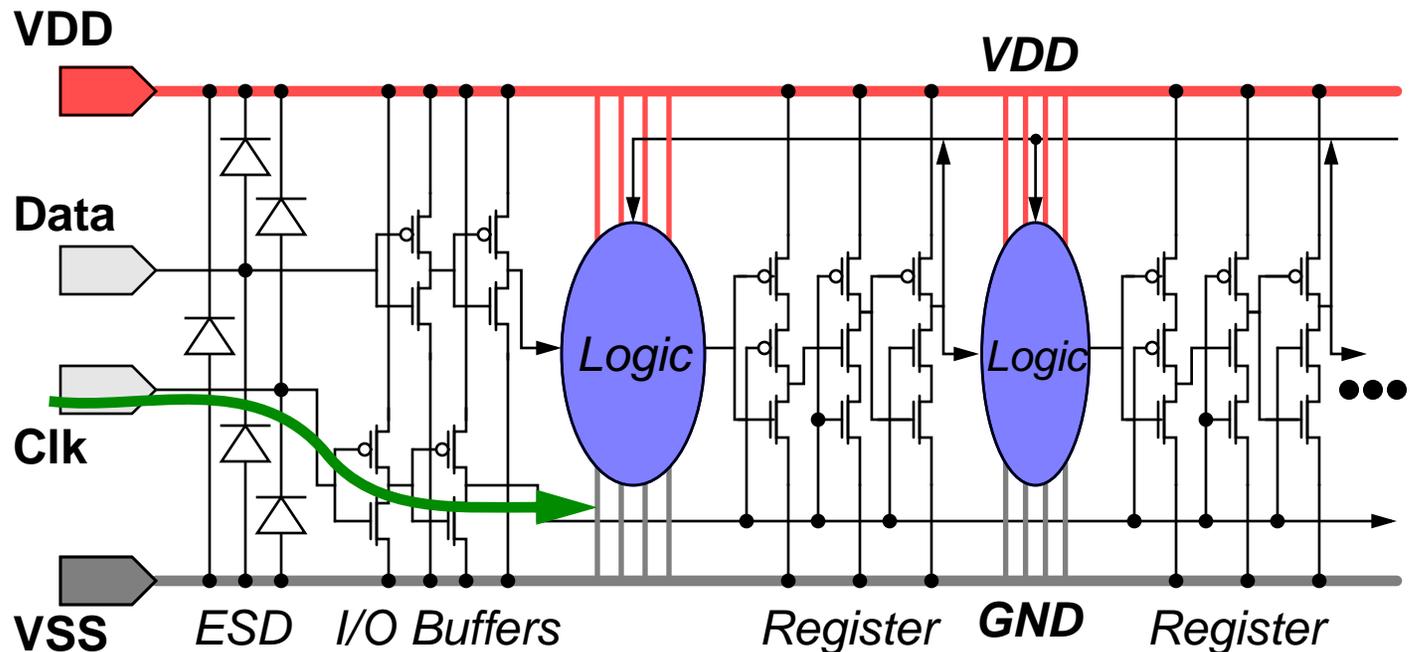


- Data must not transition near clock edges
- *Corollary:* Perturbations on clock network (e.g., noise spikes, thermal-related delays) achieve same results



Circuit Integrity: *Clock*

How To Make This System Fail ...

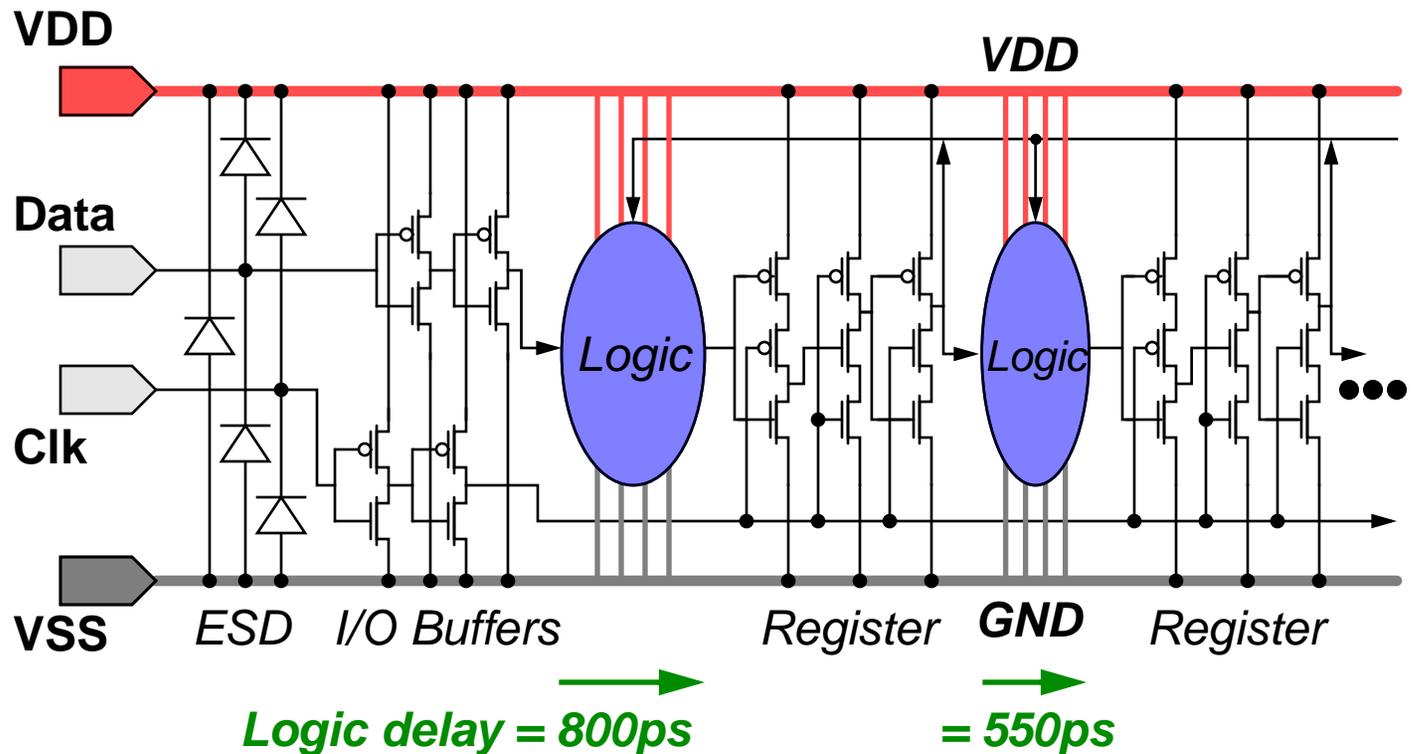


- RF that makes it this far (past initial I/O buffers) has corrupted the system: packet-encoding techniques that might detect data corruption are inapplicable
- Unwanted clock edges likely result in metastability, lead to incorrect results, most likely system crash



Circuit Integrity: *Clock*

Maximum clock-frequency calculations

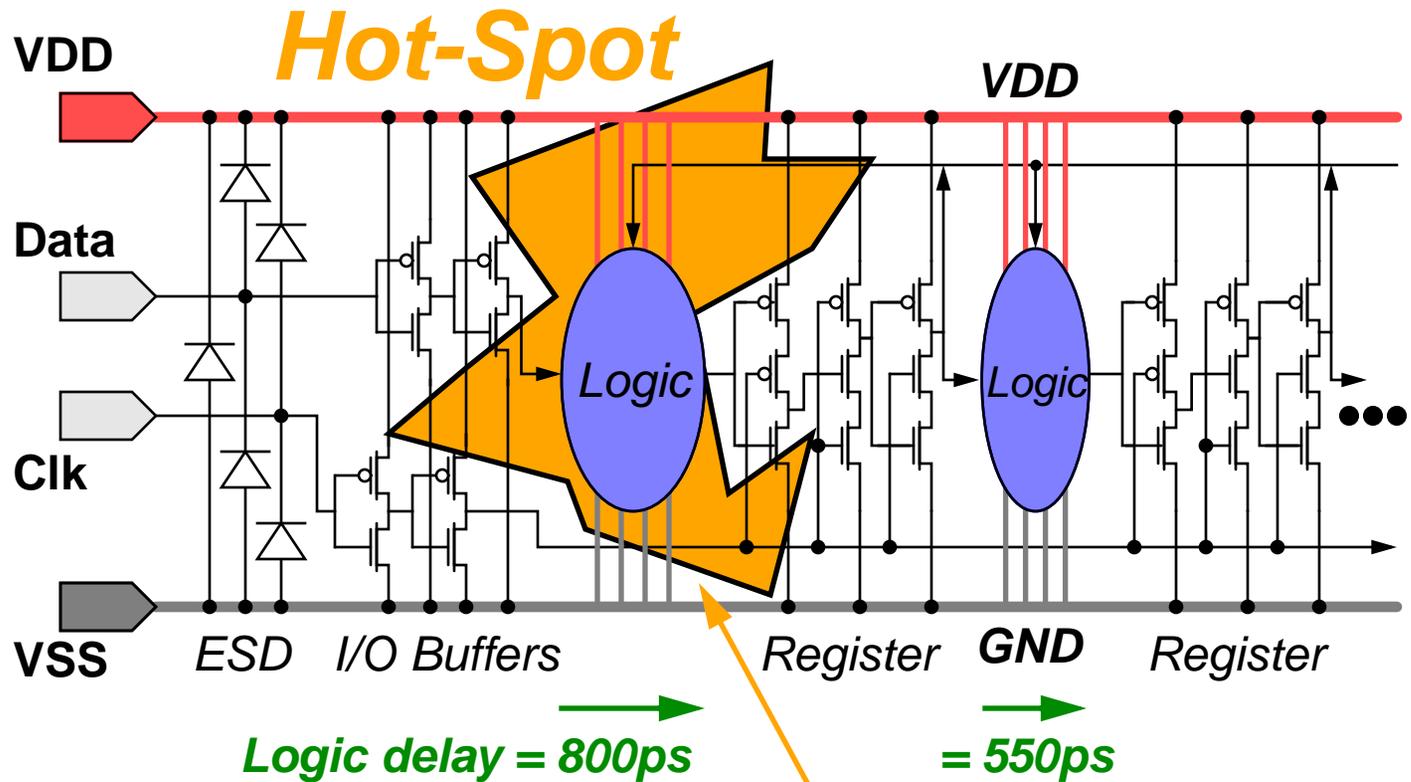


- Critical path determines minimum clock period (in this example: 800ps + register overhead + skew/etc. = 1000ps total, or 1GHz [as opposed to 750ps/1.33GHz])



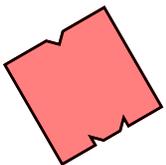
Circuit Integrity: *Clock*

How To Make This System Fail ...



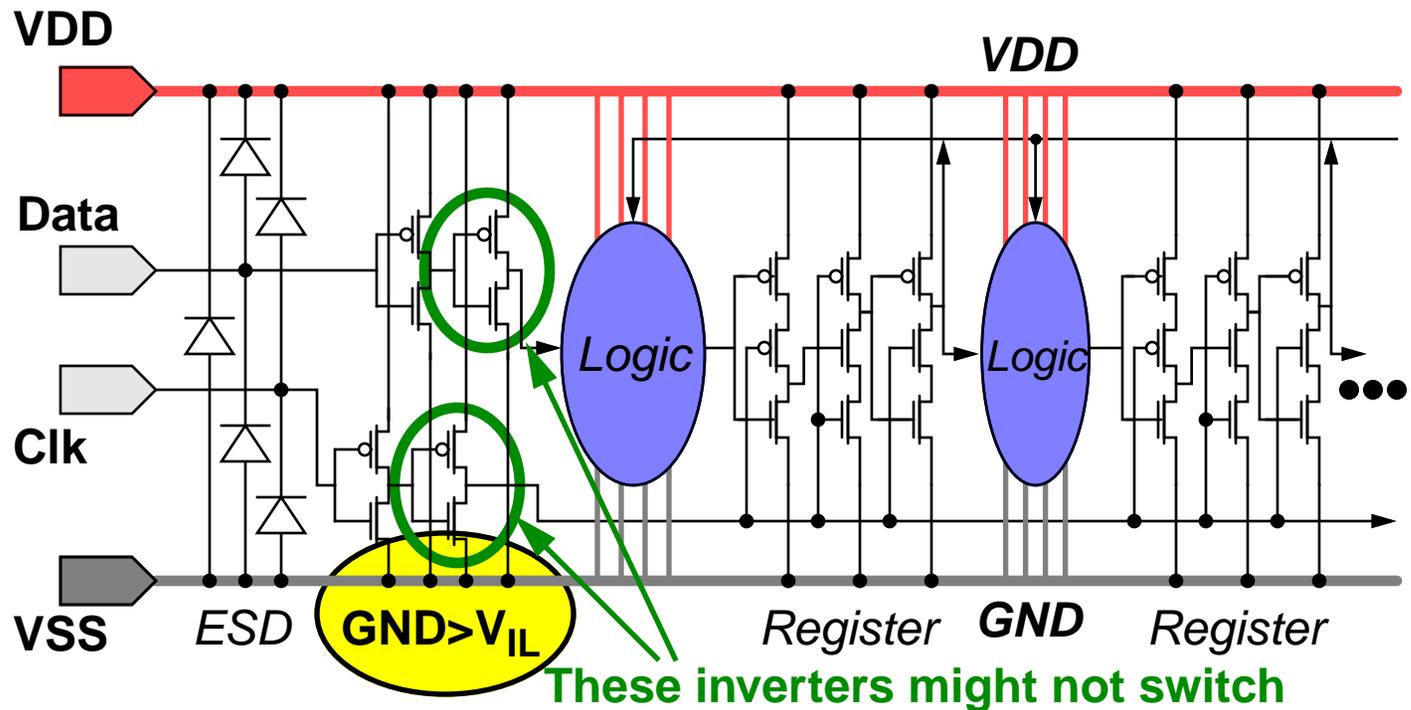
This portion of the system logic heats up, experiences more delay than other areas

- Thermal gradients in synchronous systems disastrous (consider tight timing margins in GHz systems)

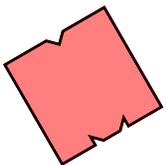


Circuit Integrity: V_{DD} & V_{SS}

How To Make This System Fail ...



- Localized (or global) ripples on groundplanes can cause logic to misbehave, inputs to be misinterpreted (e.g. suppose Data/Clk = 1, $V > V_{IL}$ on gate of 2nd INV)
- Causes same effects as data/clock corruption



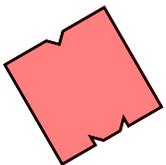
Circuit Integrity

DISTINGUISHING CHARACTERISTICS of the NETWORKS in DIGITAL SYSTEMS:

- **CLK: Only Edges Matter**
- **DATA: Both Timing and Levels Matter**
- **VDD/GND: Even Small Changes in Level (e.g., 5–10%) Matter**

CLK/DATA: Enter Via ESD Protection

VDD/GND: 1/2 ESD (shunts one to other)

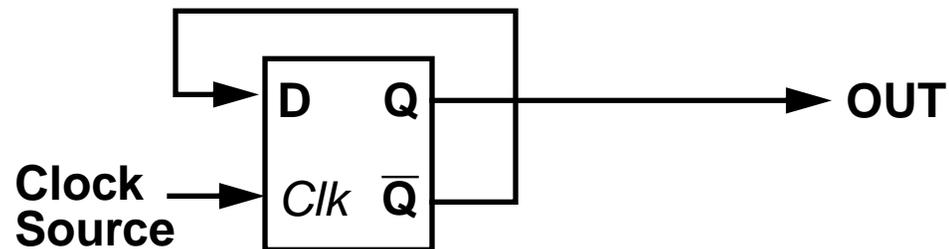


Our Research Question

Comparing CLK and DATA inputs, which is more important:

- The distinguishing characteristics of the way those inputs will be used in the digital system or circuit?
- The levels and frequencies of injected RF?

Our Device Under Test (counter):

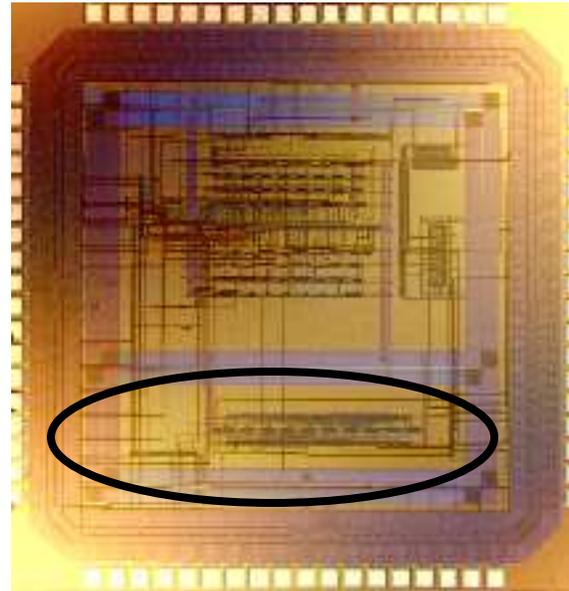


Just about simplest possible digital system

**[Last Year's Results: evaluated
vulnerability of CLK input]**



Our Device Under Test

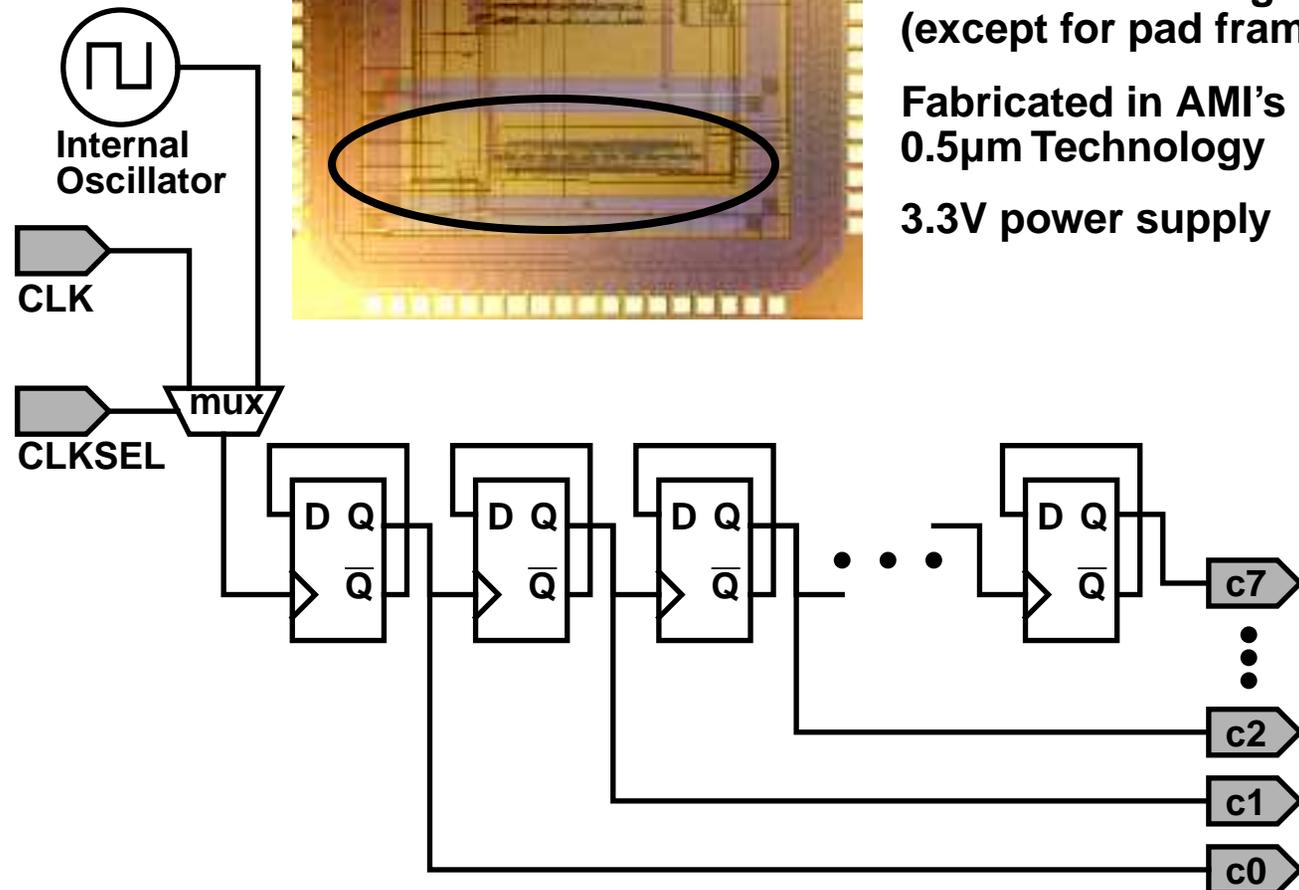


**8-bit Ripple Counter,
Chip Built via Mosis**

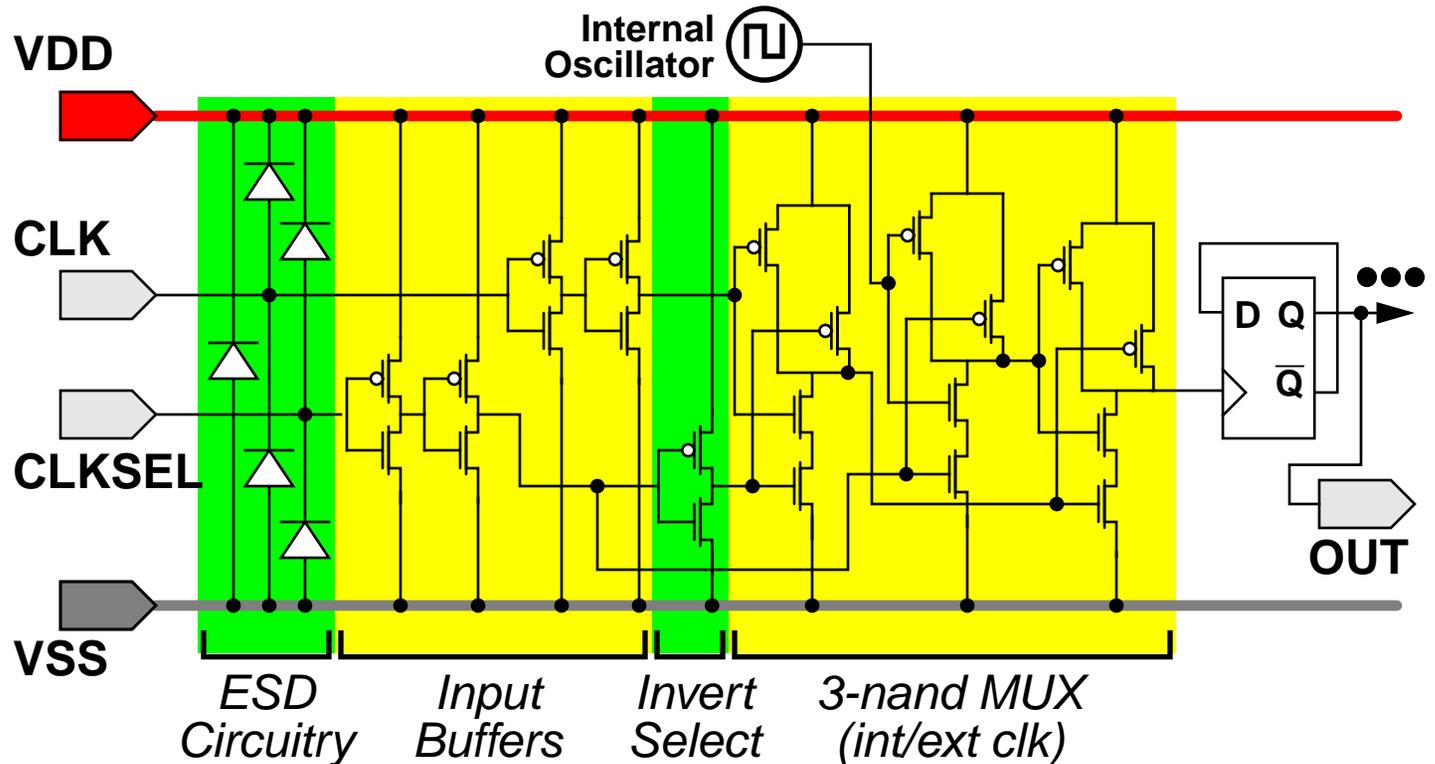
**Full-Custom Design
(except for pad frame)**

**Fabricated in AMI's
0.5 μ m Technology**

3.3V power supply

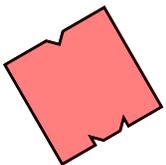


Our Device Under Test

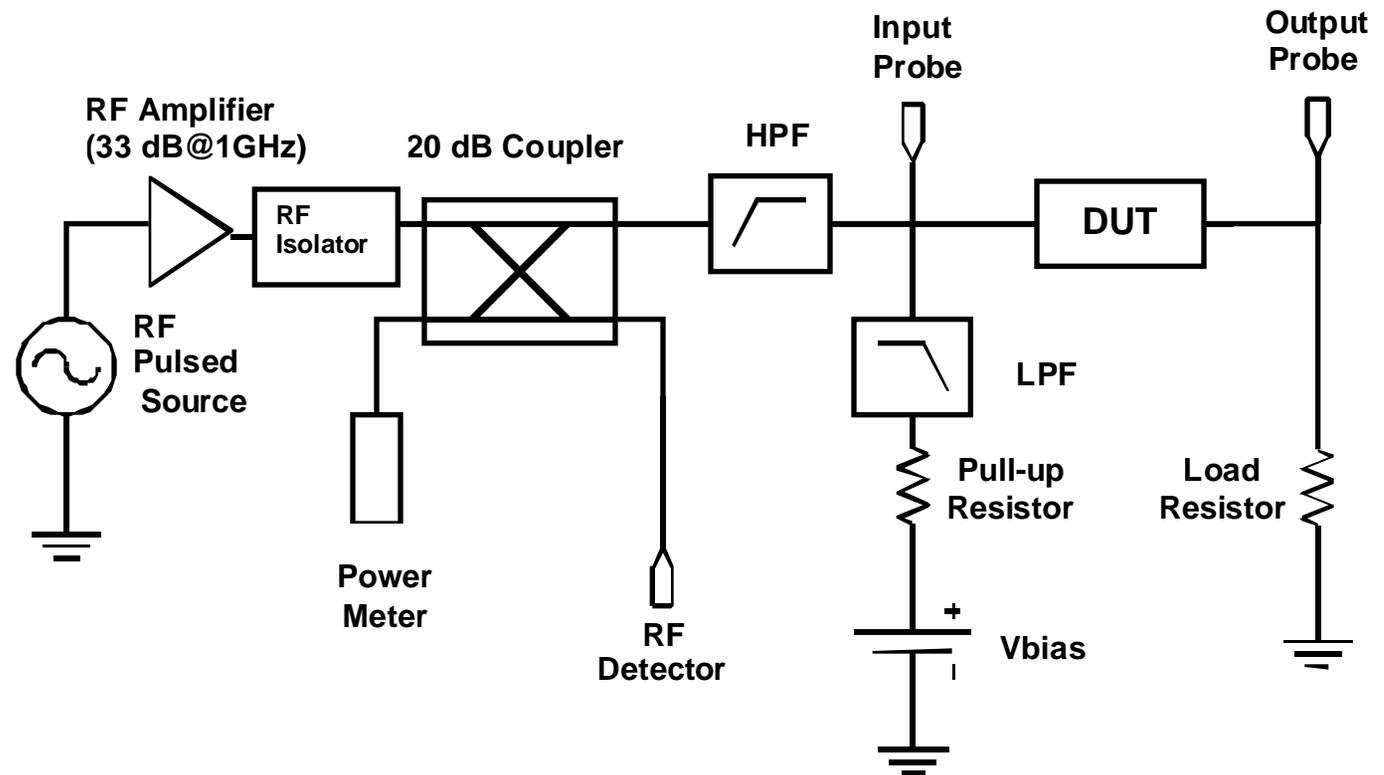


Points of Interest:

- Digital system built from complementary gate designs (high input impedance, low output impedance).
- CLK only driving MUX, one DFF (see *previous slide*).
- => CLK and CLKSEL see virtually identical loads.

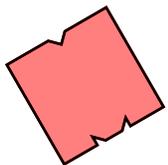


Experimental RF Set-Up

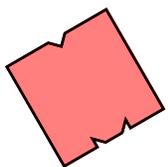
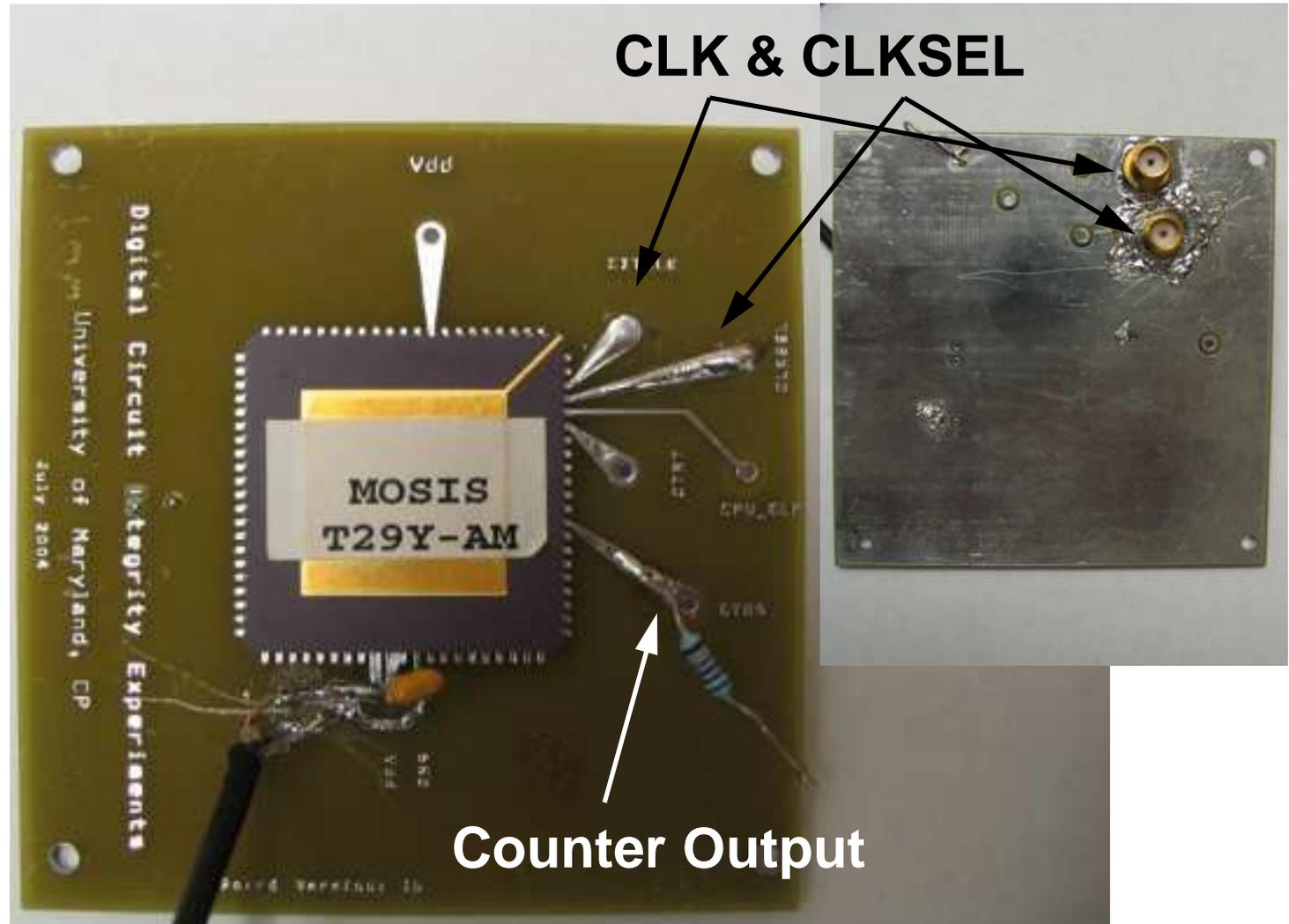


Power Amp 33dB at 1GHz

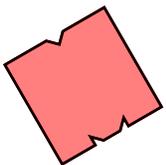
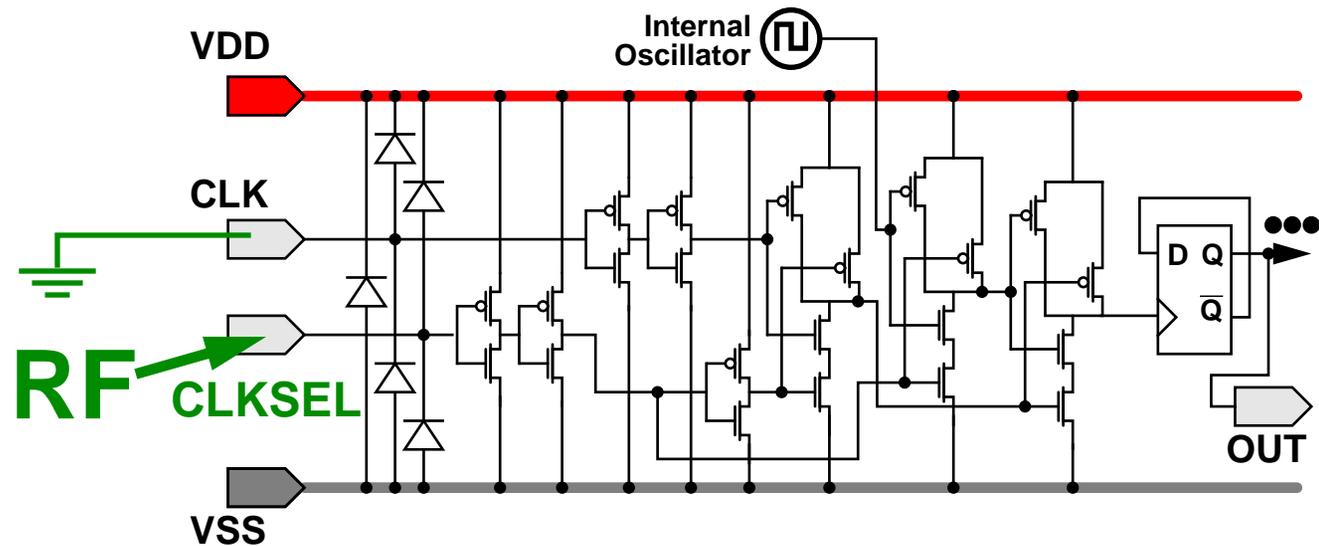
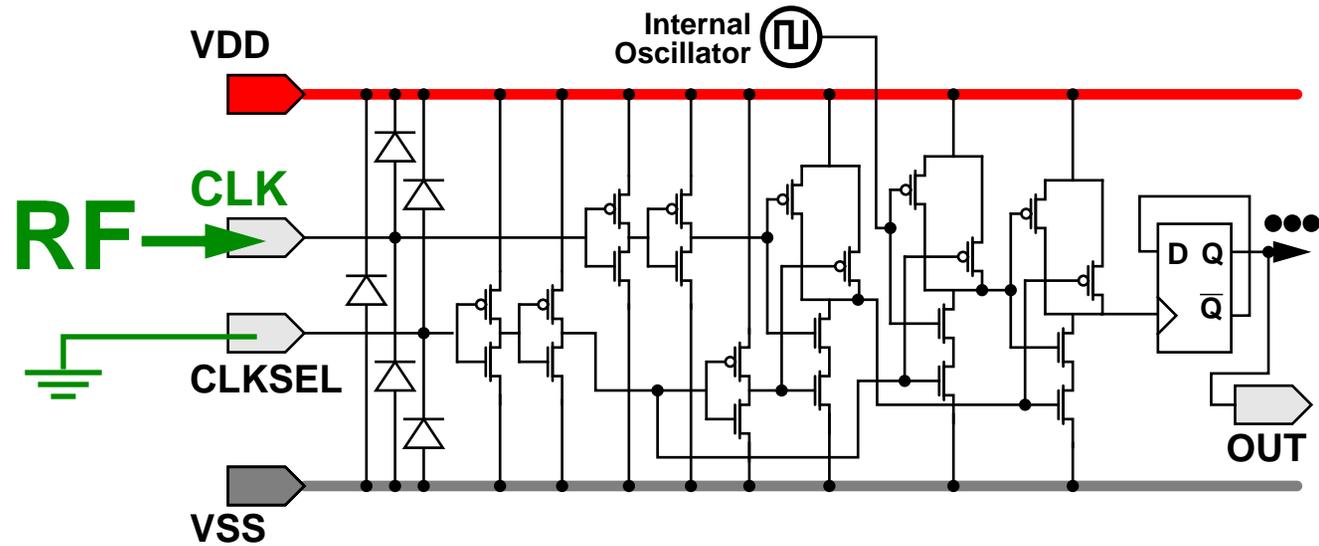
Freq 800MHz – 4.2Ghz with 1.2W max power



Test Board

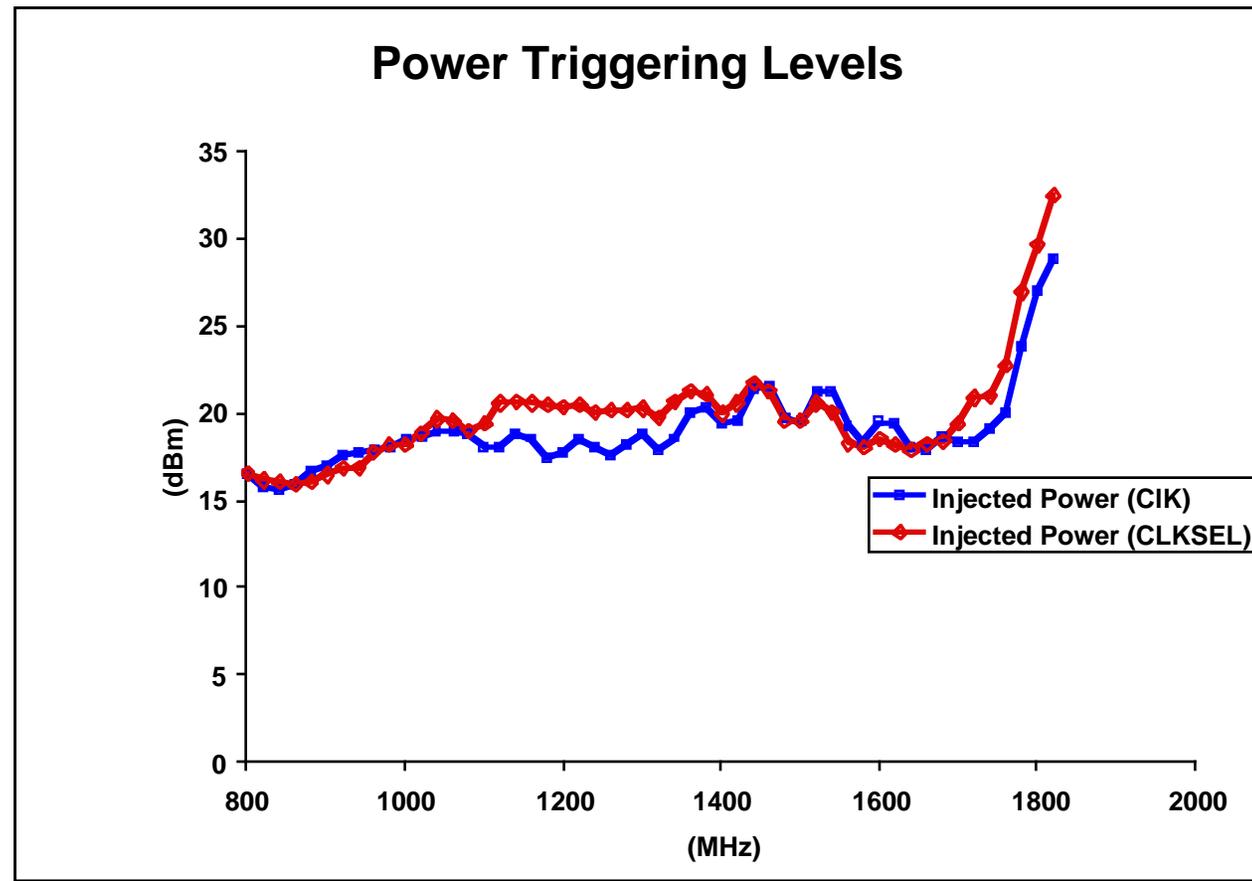


Test Scenarios



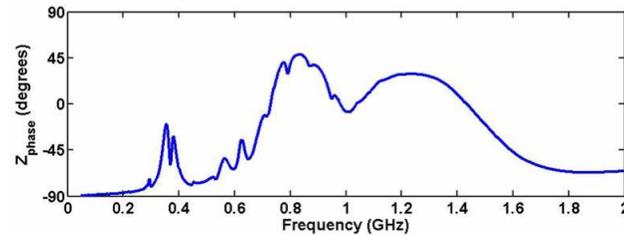
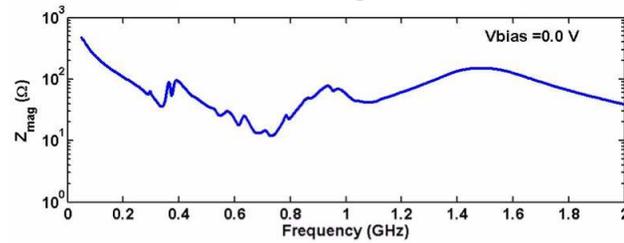
CLK vs. CLKSEL Inputs

Power-v-Freq. required to cause incorrect behavior (state change in digital logic)

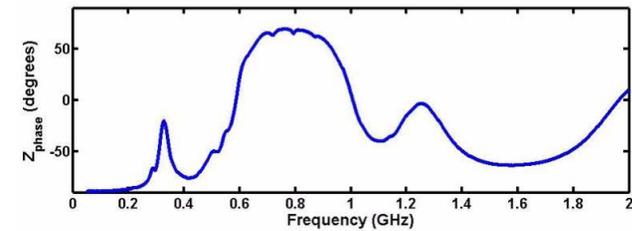
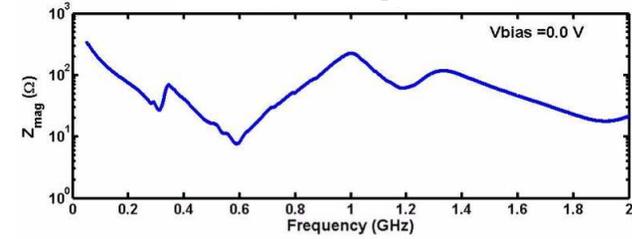


Input Impedance

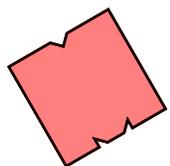
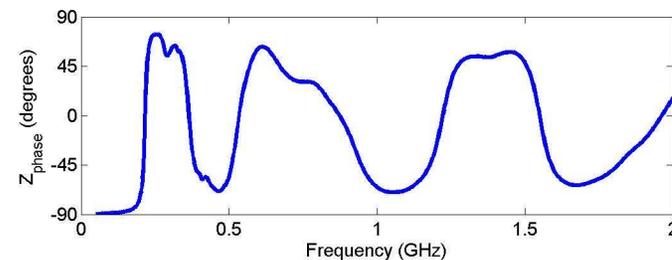
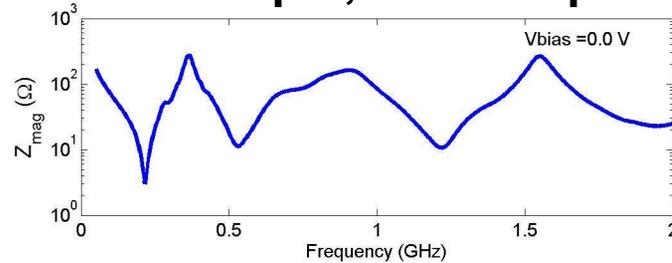
CLK pin



CLKSEL pin

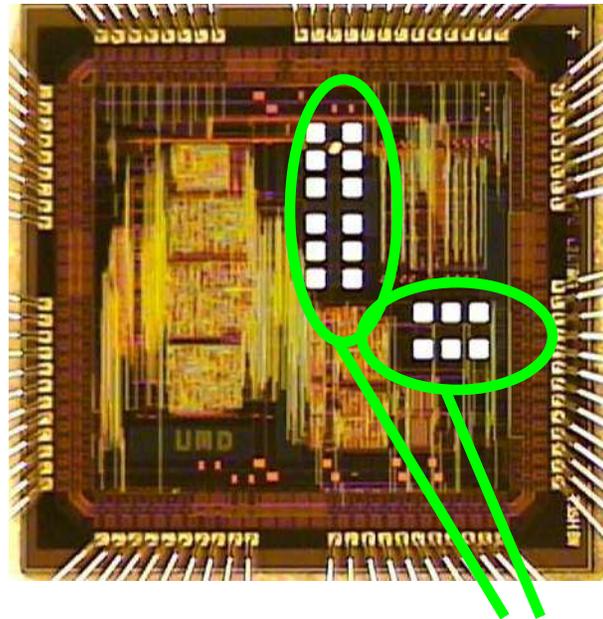


CLK pin, old set-up

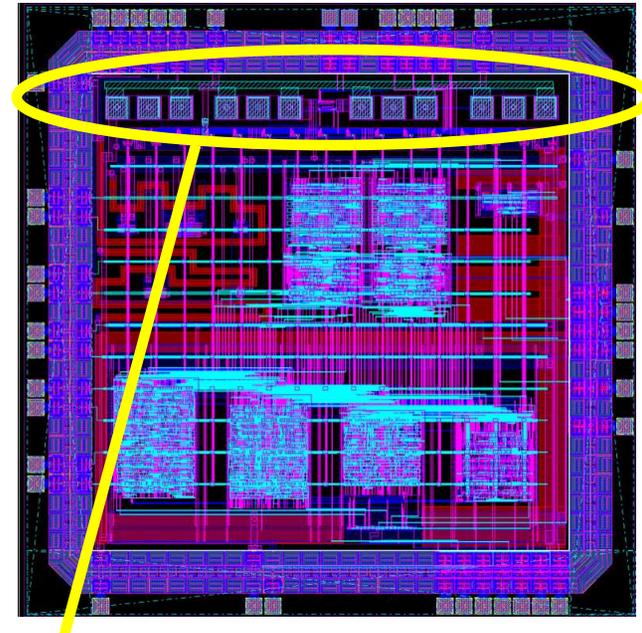


Recent Work: ESD

ESD Test Chip I (die photo)
for Rodgers & Firestone



ESD Test Chip II (layout)
for Rodgers & Firestone



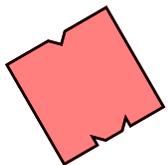
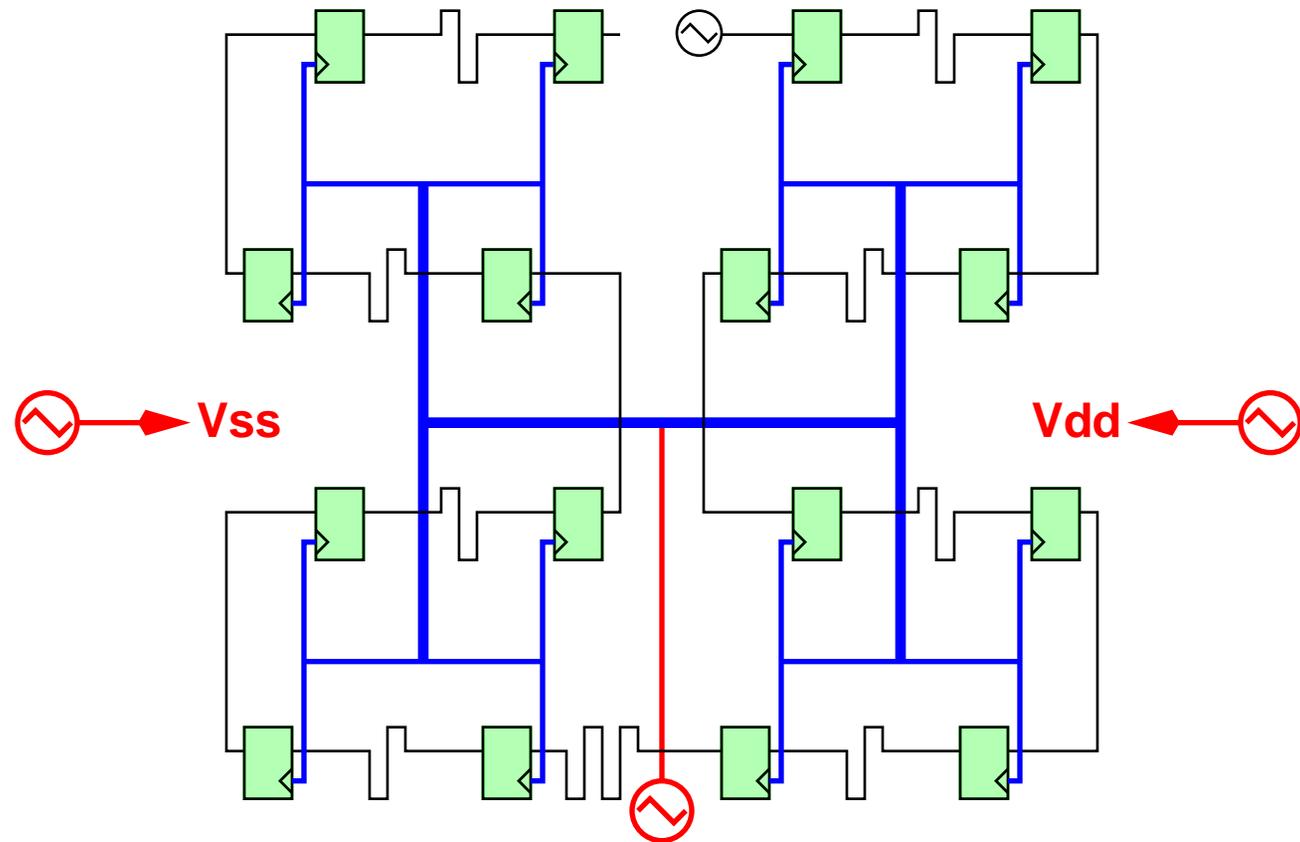
Custom-designed on-chip pads to accommodate input probes

Designed & fabricated two chips (one on right just back from fab) ... allow probing at various points between PAD and internals



Future Work

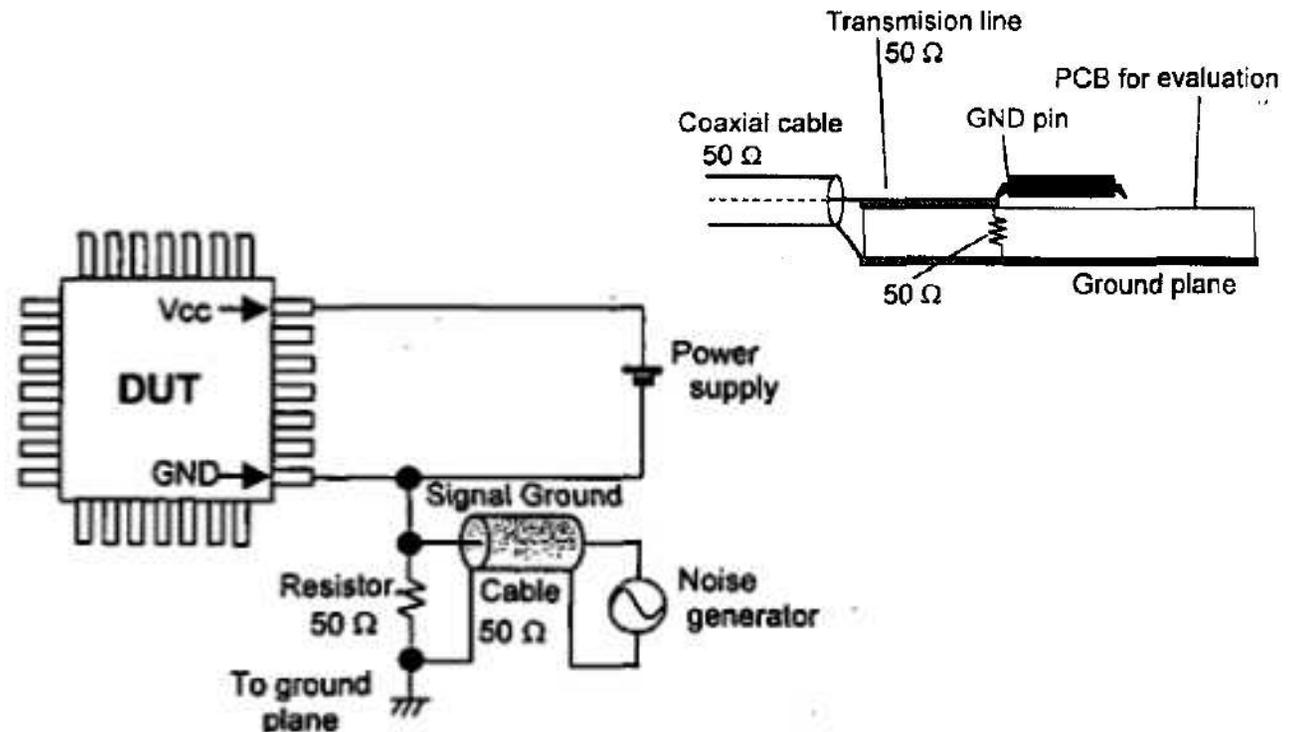
New Test Structures (e.g., to emulate larger designs, differentiate between CLK & DATA)



Future Work

Using same board, test the power rail

Design new board that differentiates GND input pin from IC's ground plane, to test the ground pin's susceptibility



Acknowledgments, etc.

GRAD STUDENTS:

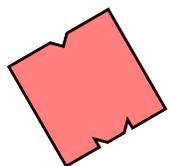
**Vincent Chan, Cagdas Dirik,
Samuel Rodriguez, Hongxia Wang**

INVALUABLE AID:

Todd Firestone and John Rodgers

FOR MORE INFO:

**<http://www.ece.umd.edu/~blj/integrity>
blj@umd.edu**

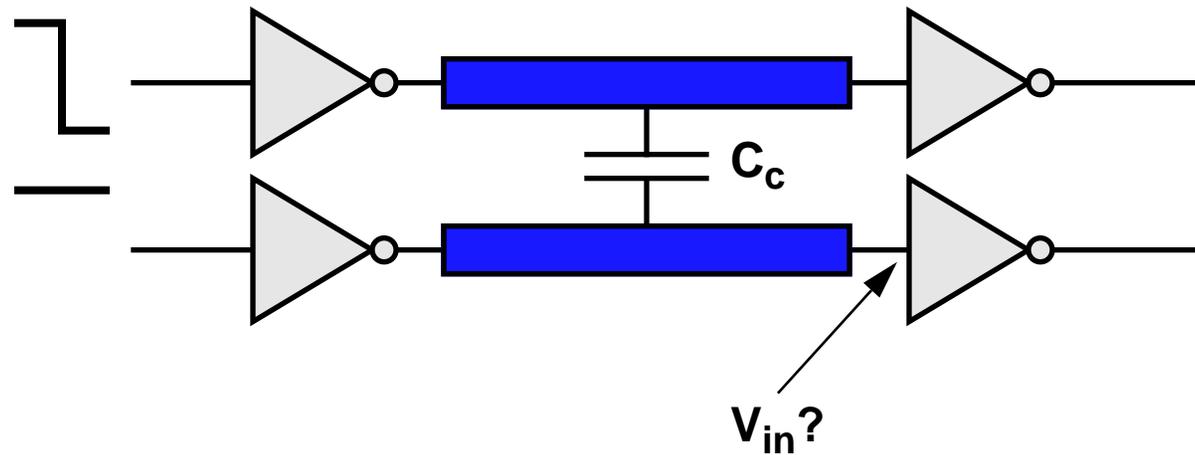


Capacitive Parasitics

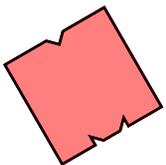
CROSS TALK

Largely capacitive at current switching speeds ... inductive coupling is major concern in I/O of mixed signal circuits (e.g. RF).

Translation: *pay attention to the cut-off frequency.*



In general, $V_{in} \neq 0$

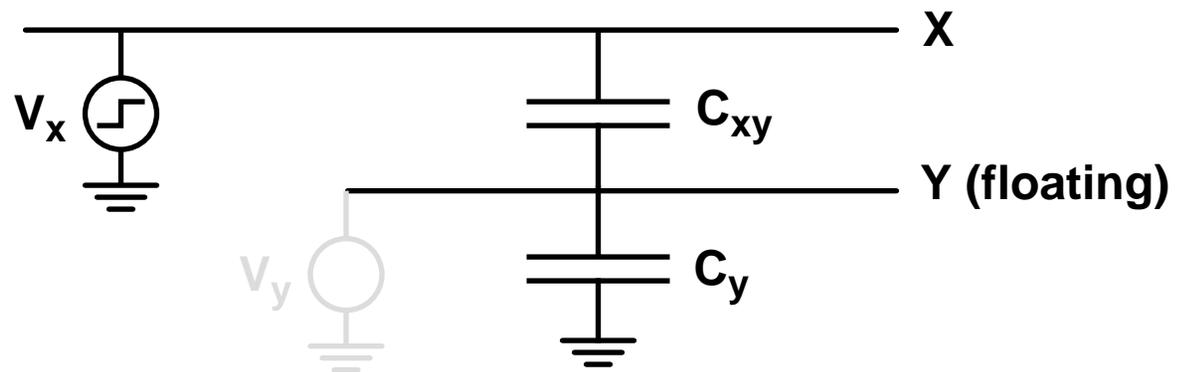


Capacitive Coupling

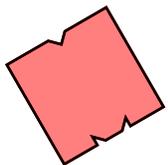
Influenced by *impedance* of coupled line:

- Wire Y is **driven**: ΔV_y is **transient**
- Wire Y is **floating**: ΔV_y is ***persistent***

Floating:



$$\Delta V_y = \Delta V_x \cdot \frac{C_{xy}}{C_y + C_{xy}}$$

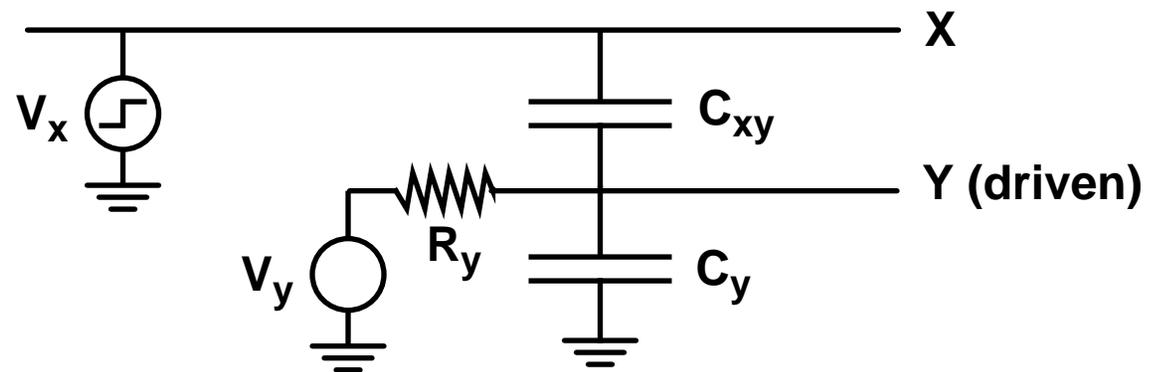


Capacitive Coupling

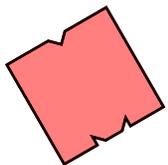
Influenced by *impedance* of coupled line:

- Wire Y is **driven**: ΔV_y is **transient**
- Wire Y is **floating**: ΔV_y is ***persistent***

Driven:

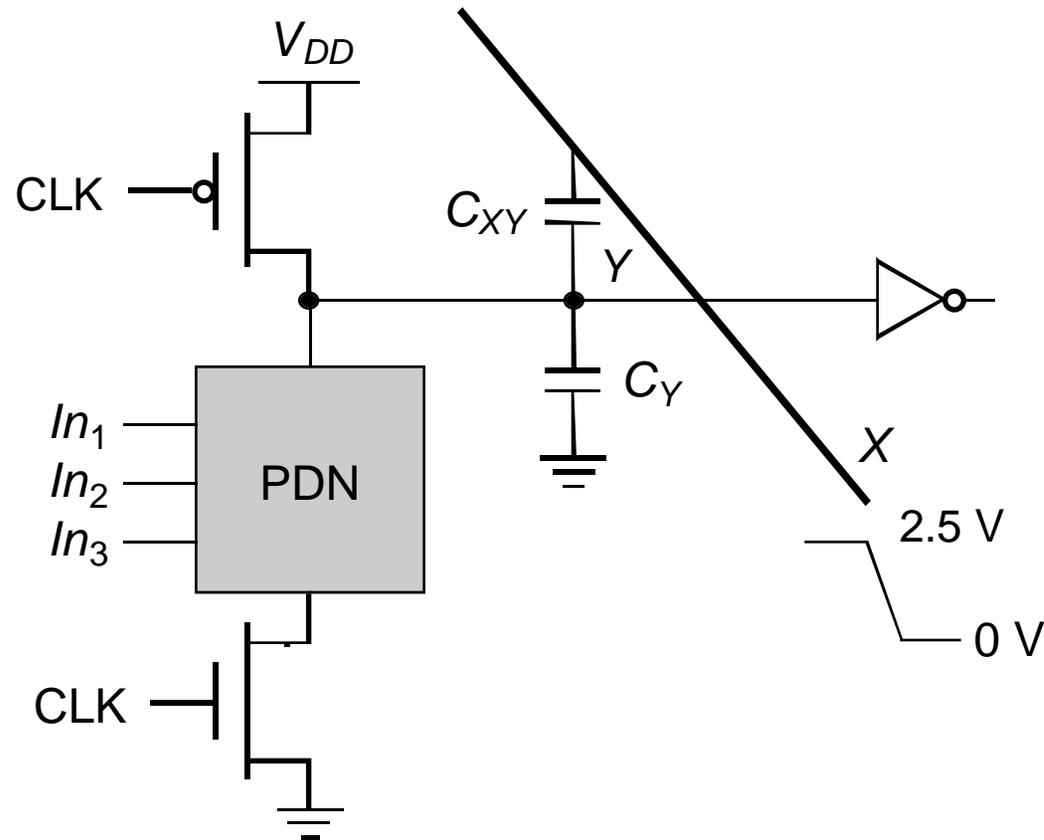


$$\Delta V_y = \Delta V_x \cdot \frac{Z_y \cdot C_{xy}}{t_{\text{rise}}}$$

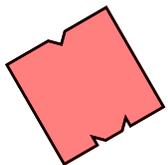


Floating-Coupling Example

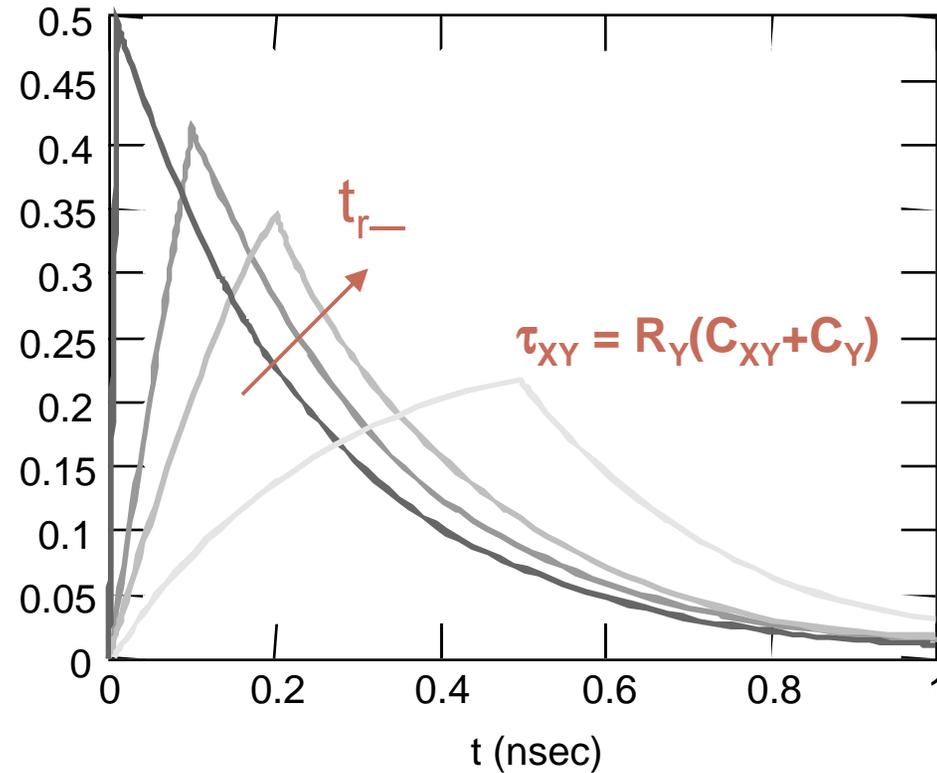
X is (logically unrelated) wire crossing over circuit in the metal-1 layer. Because this is a dynamic circuit, the output is floating when PDN=>>false. Example assumes capacitance to poly wire Y (gate for inverter); node Y is precharged during PRE stage to 2.5V, wire X undergoes 2.5 -> 0V.



3 x 1 μm overlap: 0.19 V disturbance

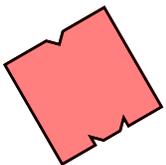


Driven-Coupling Example



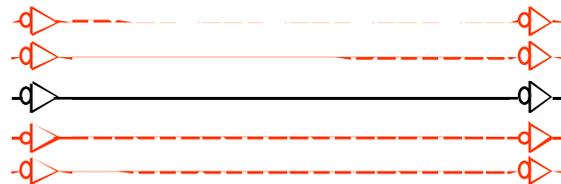
Transient decays with time constant

$$\tau_{xy} = R_y(C_{xy} + C_y)$$

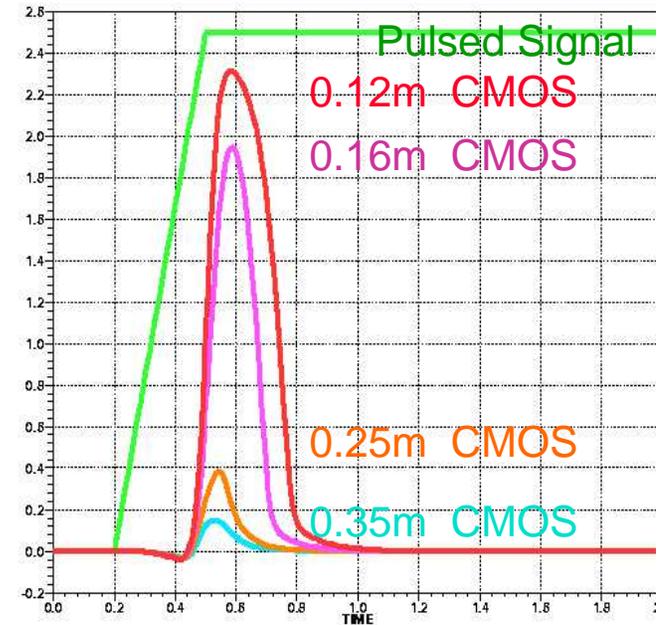


Crosstalk & Technology

Crosstalk vs. Technology

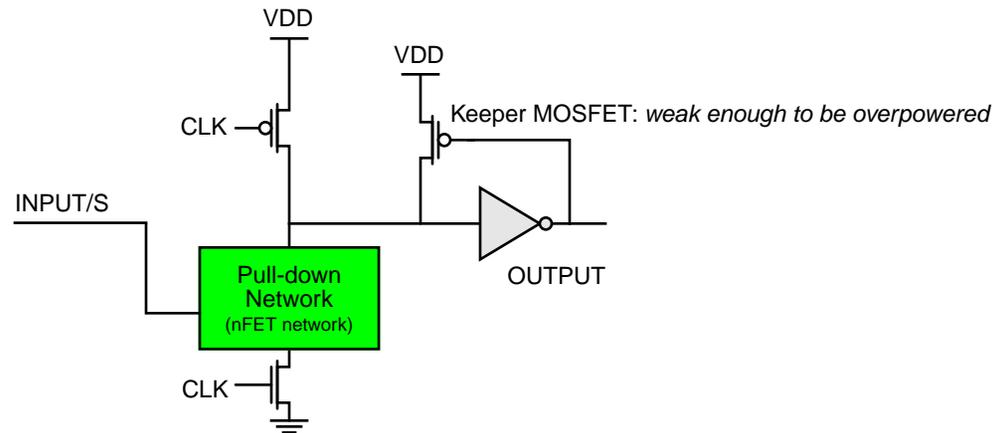


Black line quiet ————
Red lines pulsed - - - - -
Glitches strength vs technology



Some Solutions to Capacitive Crosstalk

- **Proportional noise source:** Increasing Vdd will not help
- **Avoid floating nodes:** use “keeper” circuits, e.g.:

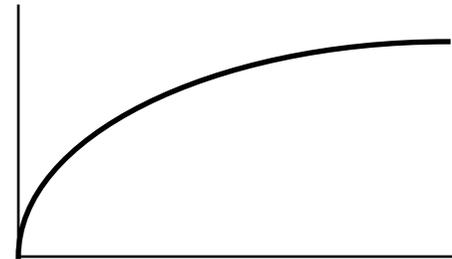
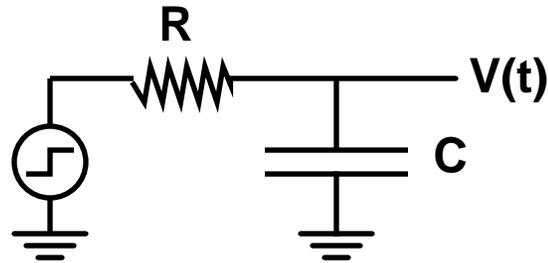


- **Keep sensitive nodes from full-swing signals**
- **Make rise/fall time large (but it can increase power)**
- **Use differential signaling: turns cross-talk into “common-mode” noise source**
- **Don’t have long parallel wires**
- **Wires on adjacent metal levels: *perpendicular***
- **Shield wires by inserting VDD/GND wires between (works in same plane as well as in vertical dimension)**

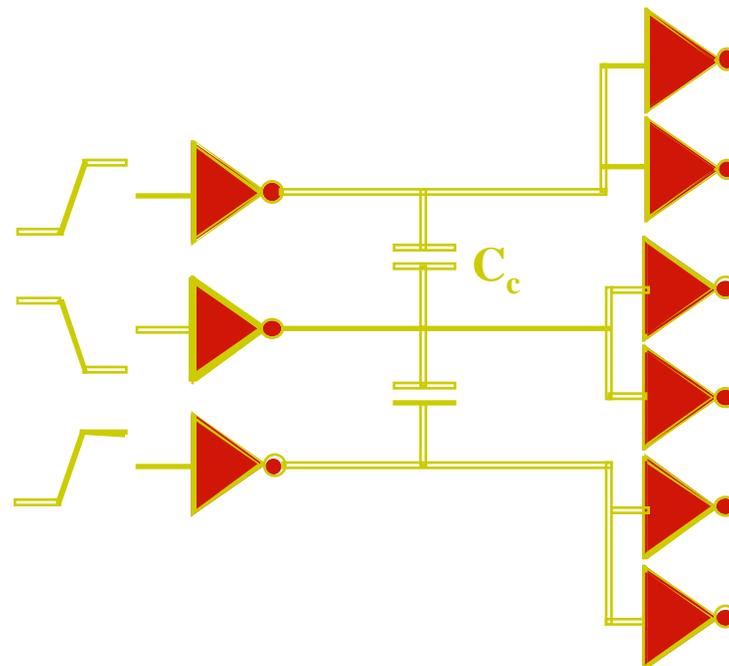


Capacitance & Wire Delays

Recall rise time:



What if C is not a constant?



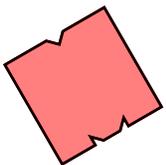
Miller Effect

Both terminals of capacitor are switched in opposite directions
($0 \rightarrow V_{dd}$, $V_{dd} \rightarrow 0$)

Effective voltage is doubled and additional charge is needed
(from $Q=CV$)

Bottom Line:

RC time constant doubles.



Capacitance & Wire Delays

- r is ratio between capacitance to neighbor and to GND:

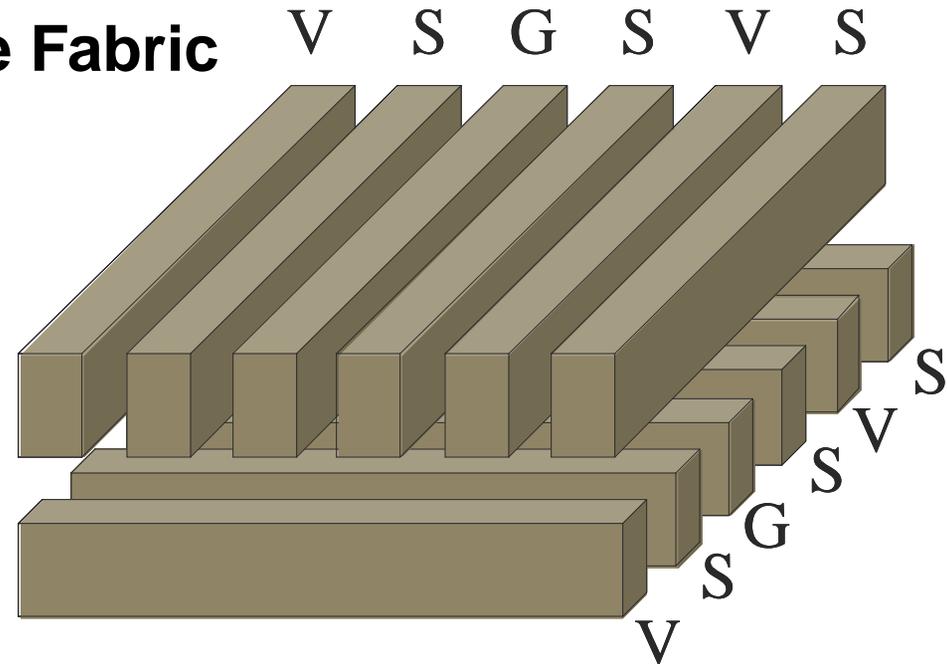
bit $k-1$	bit k	bit $k+1$	Delay factor g
↑	↑	↑	1
↑	↑	—	$1+r$
↑	↑	↓	$1+2r$
—	↑	—	$1+2r$
—	↑	↓	$1+3r$
↓	↑	↓	$1+4r$

- Wire delay may vary over 500% between worst & best case, due solely to activity on wires



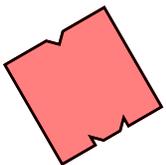
Solutions to Wire-Delay Prob.

Dense Wire Fabric

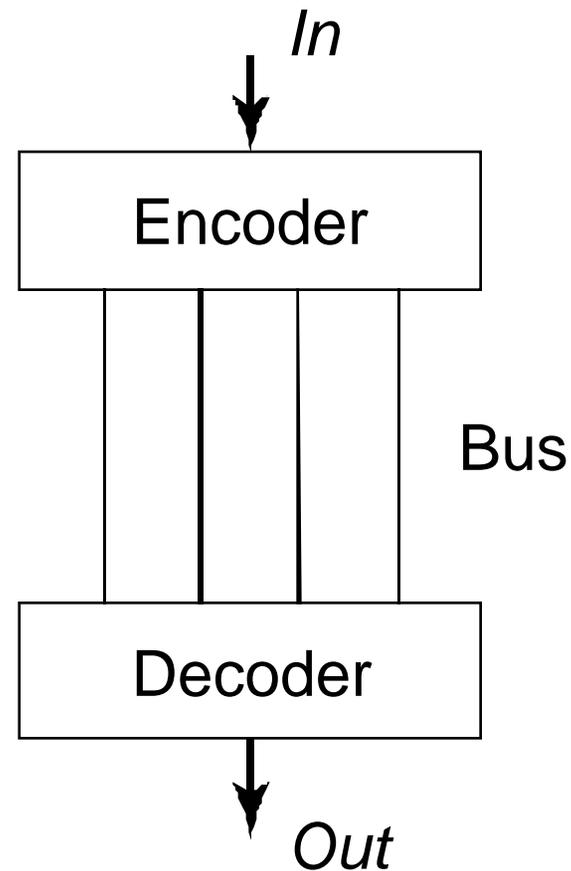


Trade-off:

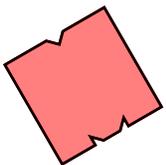
- **Cross-coupling capacitance 40x lower, 2% delay variation**
- **Increase in area and overall capacitance**



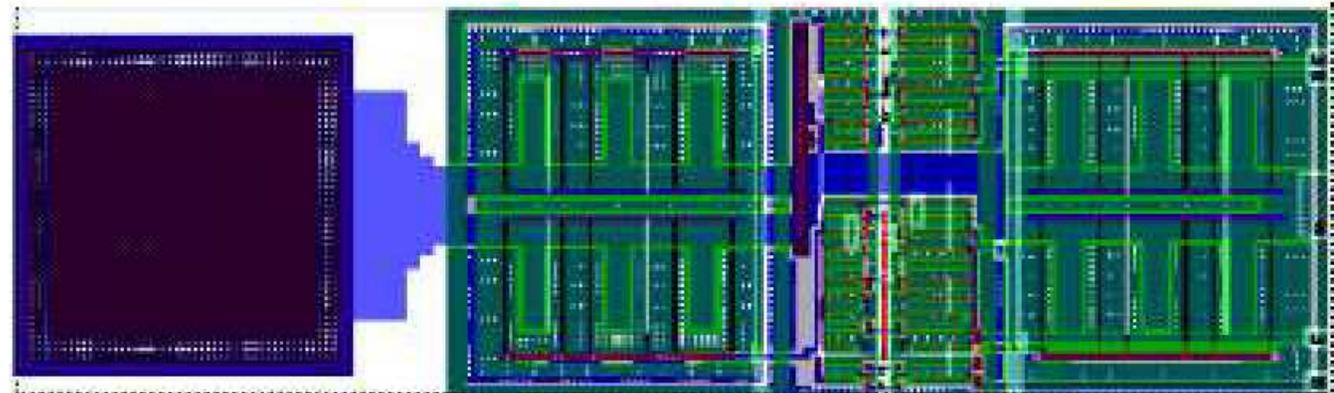
Solutions to Wire-Delay Prob.



Bus encoding to reduce “bad” transitions



I/O Pad Drivers, revisited



60–80 μm

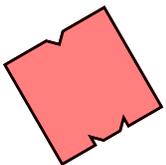
ESD
diodes

I/O
buffers

ESD
diodes

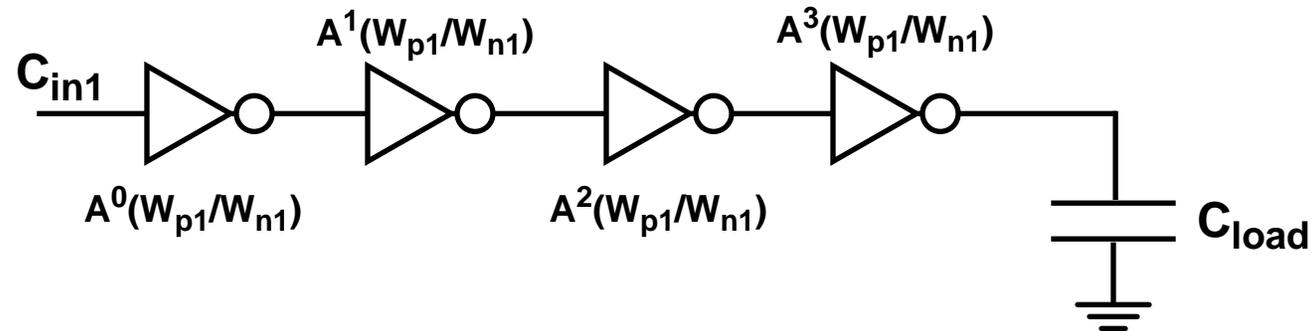
I/O Pads constrain your design:

- Enormous capacitances, require enormous gates to drive them (plus the pins & off-chip traces)
- ***This represents 1000x capacitive load of on-chip gate***
- Big gates => big currents; fast clocks => small dt ...
VDD/VSS leads have inductance => Ldi/dt noise



Transistor Sizing

Sizing for Large Capacitive Loads



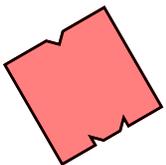
Suppose C_{load} large (e.g. bond pads, etc.)

- Scale each *inverter* (both FETs in the circuit) by a factor A (input capacitances scale by A)
- If input C to last inverter $\cdot A = C_{load}$ (i.e., C_{load} looks like $N+1^{th}$ inverter) then we have:

$$\text{Input } C \text{ of last inverter} = C_{in1} A^N = C_{load}$$

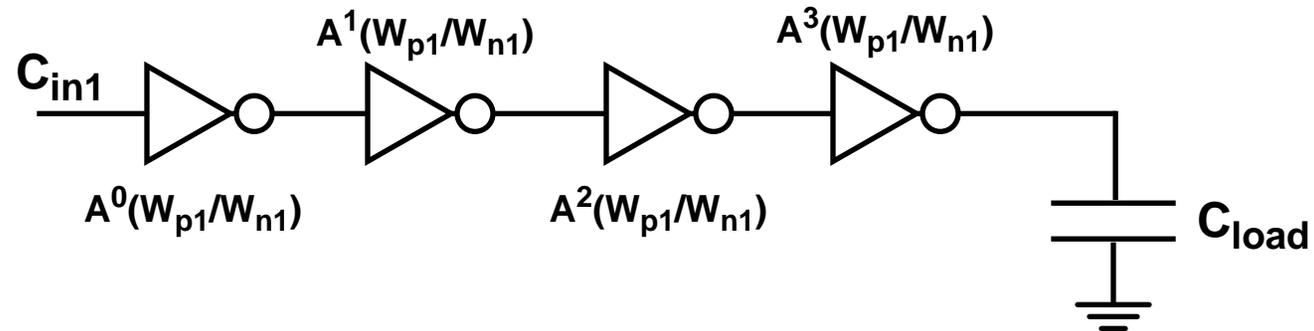
- Rearranging:

$$A = [C_{load} \div C_{in1}]^{1/N}$$



Transistor Sizing

Sizing for Large Capacitive Loads



- **Capacitances increase** by factor of A left to right
- **Resistances decrease** by factor of A left to right
- Total delay ($t_{pHL} + t_{pLH}$):

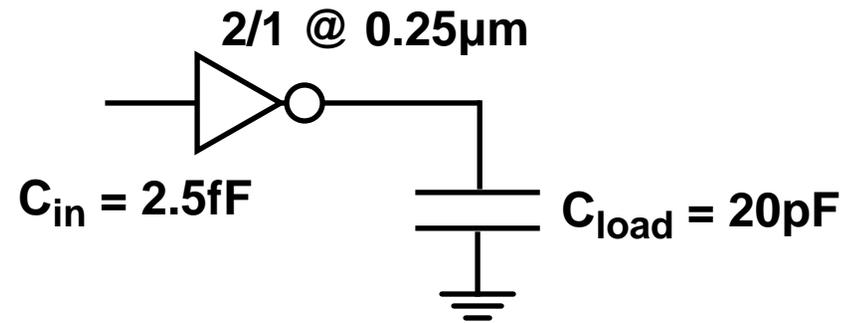
$$\begin{aligned} & (R_{n1} + R_{p1}) \cdot (C_{out1} + AC_{in1}) + \\ & (R_{n1} + R_{p1})/A \cdot (AC_{out1} + A^2C_{in1}) + \dots \\ & = N (R_{n1} + R_{p1}) \cdot (C_{out1} + AC_{in1}) \end{aligned}$$

- Find optimal chain length:

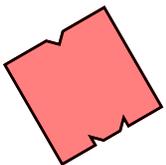
$$N_{opt} = \ln(C_{load} \div C_{in1})$$



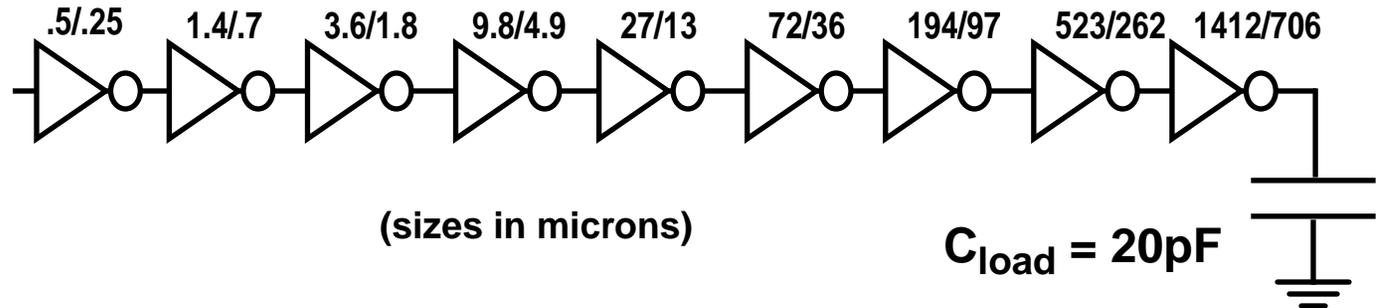
Example



Load is ~8000x that of single inverter's input capacitance: find optimal solution.



Example



$$N_{opt} = \ln(20\text{pF}/2.5\text{fF}) = 8.98 \Rightarrow 9 \text{ stages}$$

$$\text{Scaling factor } A = (20\text{pF}/2.5\text{fF})^{1/9} = 2.7$$

$$\begin{aligned} \text{Total delay} &= (t_{pHL} + t_{pLH}) \\ &= N (R_{n1} + R_{p1}) \cdot (C_{out1} + AC_{in1}) \\ &= N (R_{n1} + R_{p1}) \cdot (C_{out1} + [C_{load} \div C_{in1}]^{1/N} C_{in1}) \end{aligned}$$

$$\text{(assume } C_{in1} = 1.5C_{out1} = 2.5 \text{ fF)}$$

$$\begin{aligned} &= 9 \cdot (31/9 + 13/3) \cdot (1.85\text{fF} + 2.7 \cdot 2.5\text{fF}) \\ &= 602 \text{ ps (0.6 ns)} \end{aligned}$$



But Wait!

**You don't (necessarily) need
the optimal arrangement**

**You can (perhaps) get away with
a slower circuit**

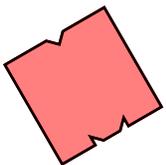
Say, for example, you want 1GHz (1ns) ...

0.6ns is overkill

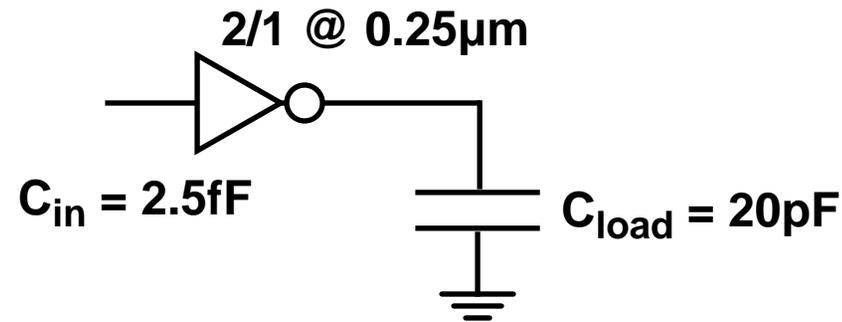
Minimize (integer) N to obey

$$\frac{t_{p,\max}}{t_{p0}} \geq \ln(\text{Fan-out}) \frac{A}{\ln(A)} = N \times \text{Fan-out}^{1/N}$$

(requires numerical methods)



Example, revisited

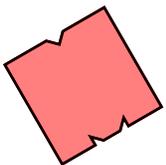


Load is ~8000x that of single inverter's input capacitance: find optimal solution.

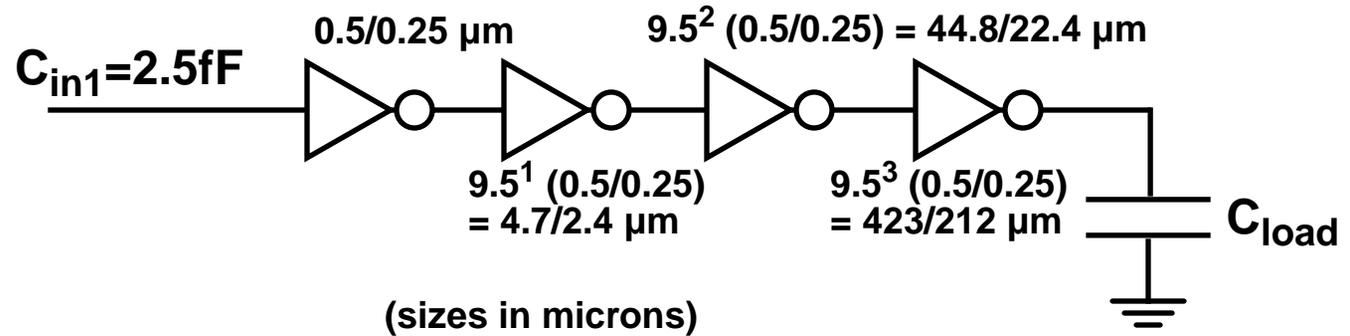
If $t_{p,max} = 1\text{ns}$ (and not 0.6ns) we can have

$N=4$

Scaling factor $A = (20\text{pF}/2.5\text{fF})^{1/4} = 9.46$



Example, revisited

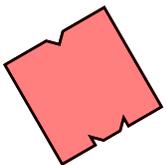


$N_{opt} \Rightarrow 4$ stages

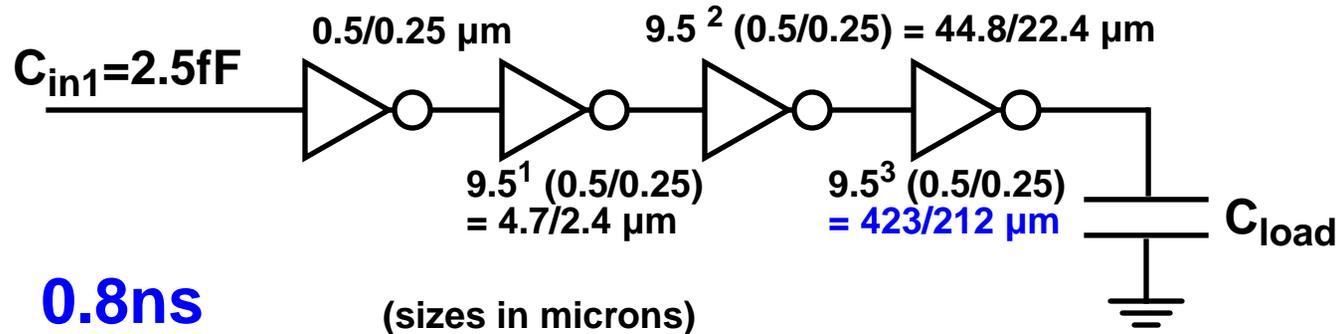
Scaling factor $A = (20 \text{ pF}/2.5 \text{ fF})^{1/4} = 9.46$

$$\begin{aligned} \text{Total delay} &= (t_{pHL} + t_{pLH}) \\ &= N (R_{n1} + R_{p1}) \cdot (C_{out1} + AC_{in1}) \\ &= N (R_{n1} + R_{p1}) \cdot (C_{out1} + [C_{load} \div C_{in1}]^{1/N} C_{in1}) \\ &\quad (\text{assume } C_{in1} = 1.5C_{out1} = 2.5 \text{ fF}) \end{aligned}$$

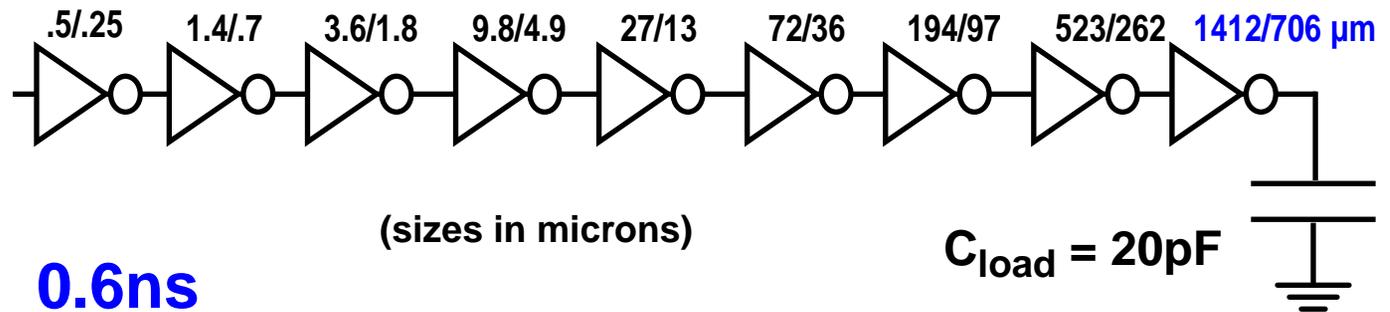
$$\begin{aligned} &= 4 \cdot (31/9 + 13/3) \cdot (1.85 \text{ fF} + 9.46 \cdot 2.5 \text{ fF}) \\ &= 793 \text{ ps (0.8 ns)} \end{aligned}$$



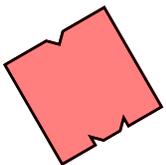
Example, revisited



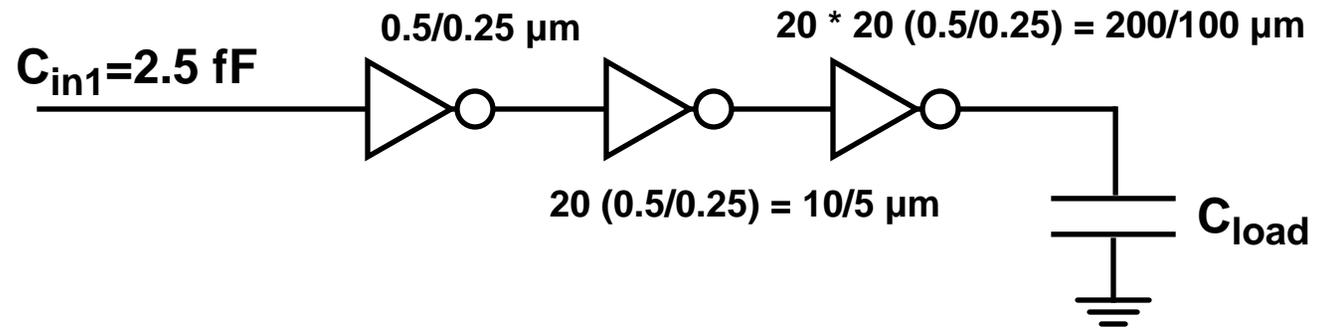
Versus:



**Reduced area, reduced current,
reduced capacitance, nearly same speed
(better parasitics, ground bounce effects)**



Can we do better?



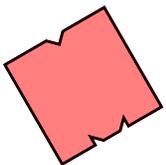
$N_{opt} \Rightarrow 3$ stages

Scaling factor $A = (20\text{pF}/2.5\text{fF})^{1/3} = 20$

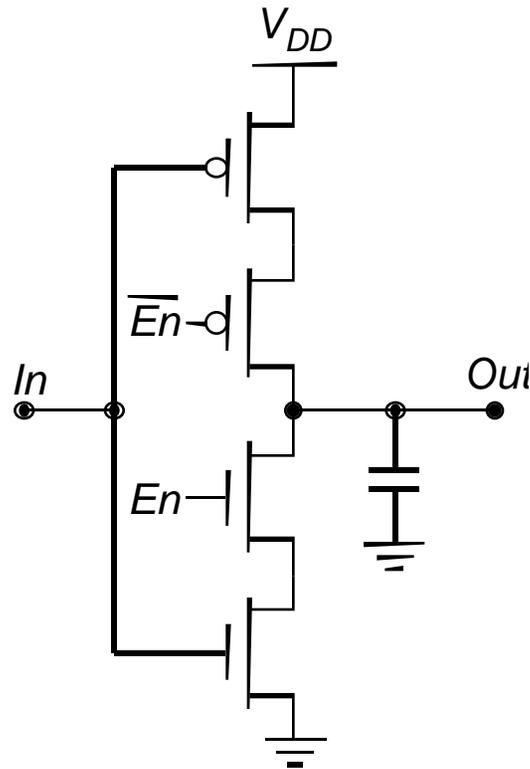
$$\begin{aligned} \text{Total delay} &= (t_{pHL} + t_{pLH}) \\ &= N (R_{n1} + R_{p1}) \cdot (C_{out1} + AC_{in1}) \\ &= N (R_{n1} + R_{p1}) \cdot (C_{out1} + [C_{load} \div C_{in1}]^{1/N} C_{in1}) \end{aligned}$$

(assume $C_{in1} = 1.5C_{out1} = 2.5 \text{ fF}$)

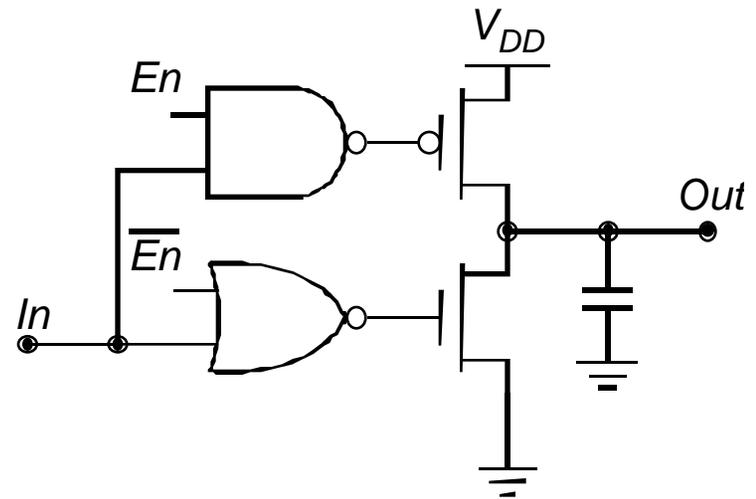
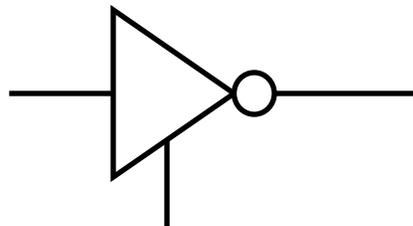
$$\begin{aligned} &= 3 \cdot (31/9 + 13/3) \cdot (1.85\text{fF} + 20 \cdot 2.5\text{fF}) \\ &= 1210 \text{ ps (1.2 ns)} \end{aligned}$$



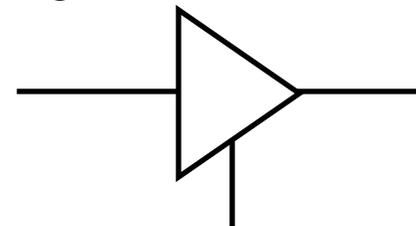
Tri-State Buffers



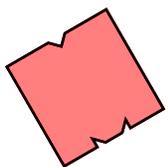
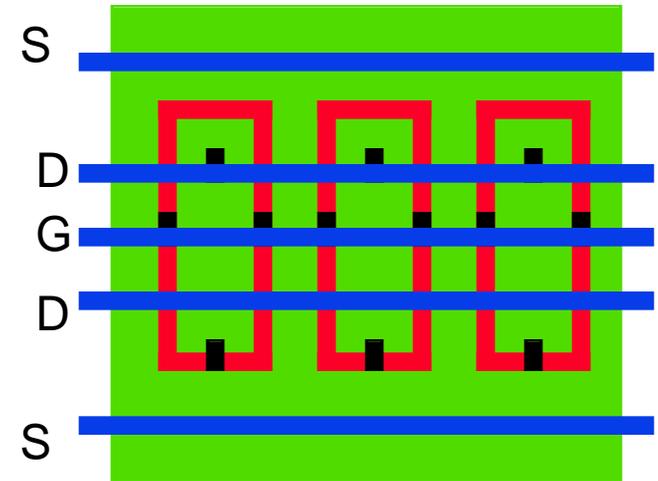
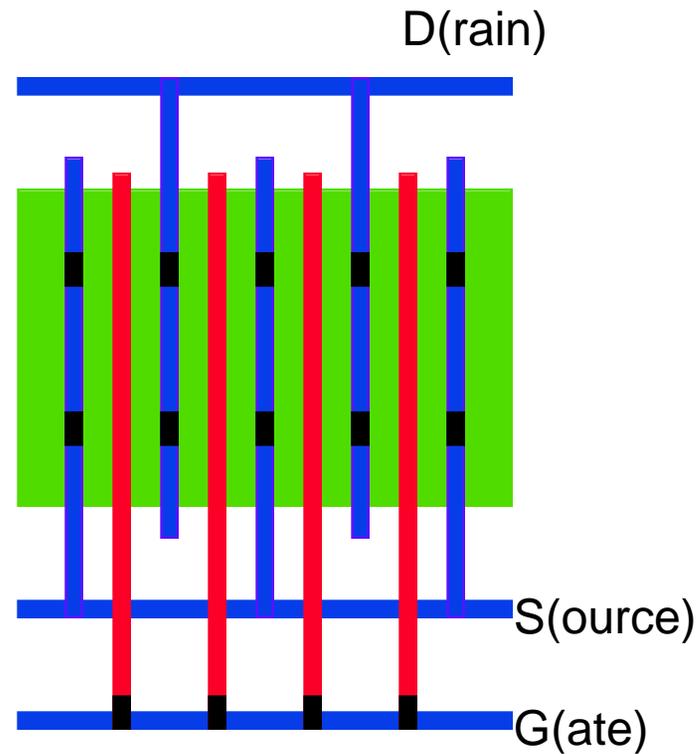
**Inverting tri-state
buffer**



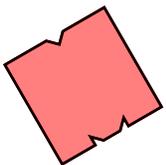
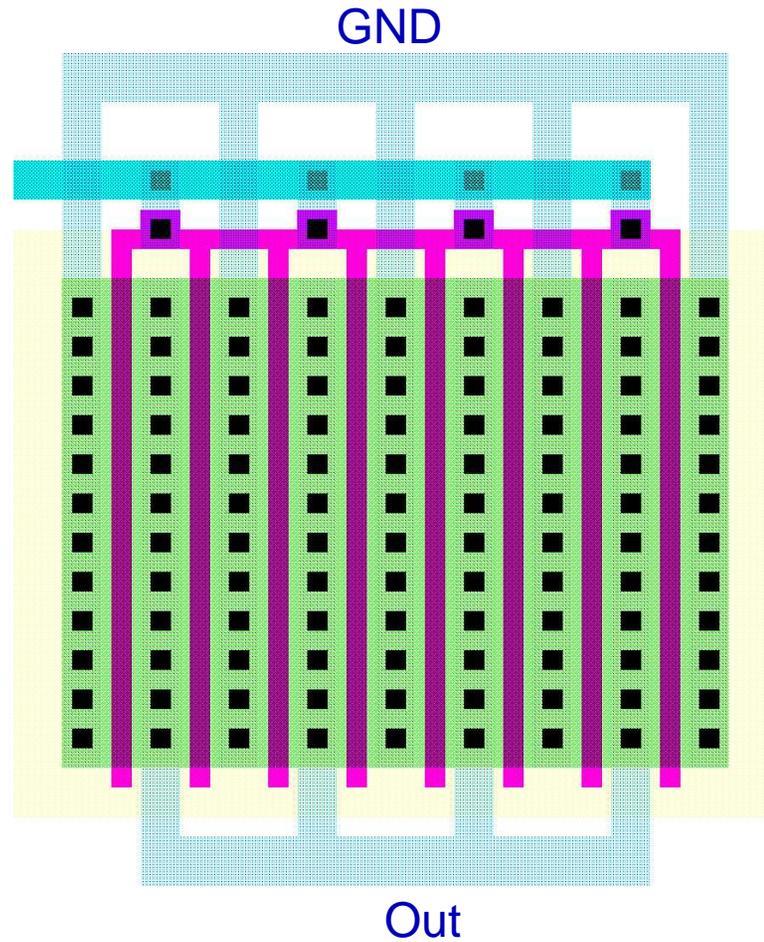
Increased output drive
**Non-inverting tri-state
buffer**



Designing Large Transistors

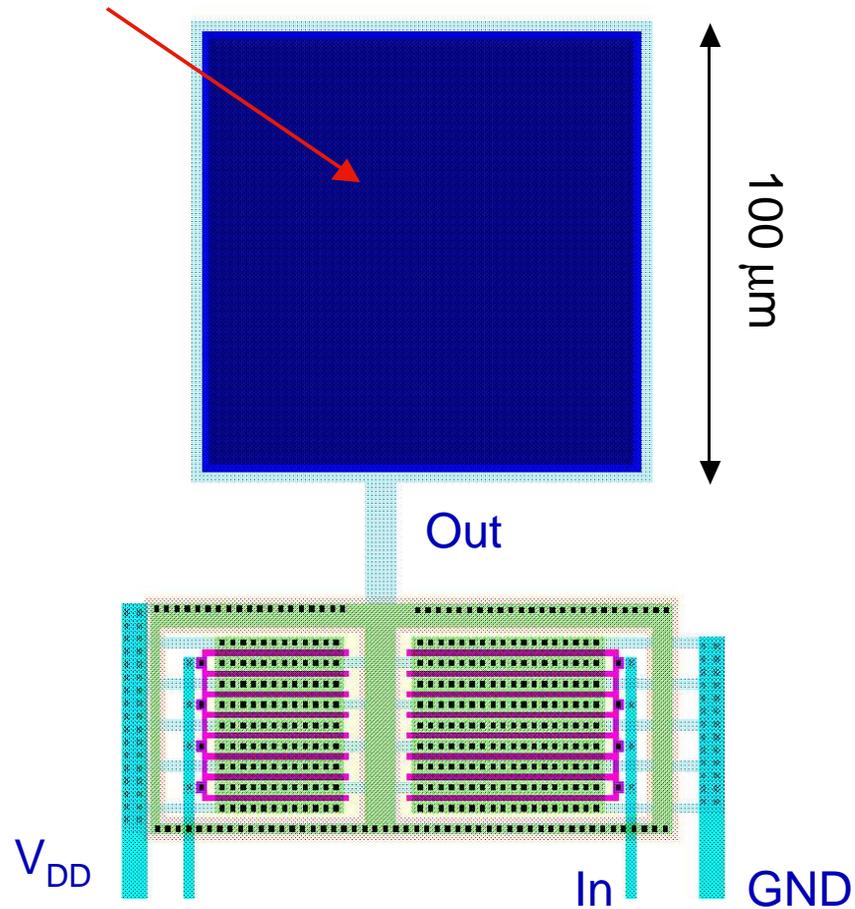


Designing Large Transistors

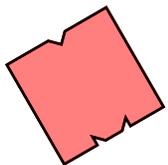


I/O Pads, again

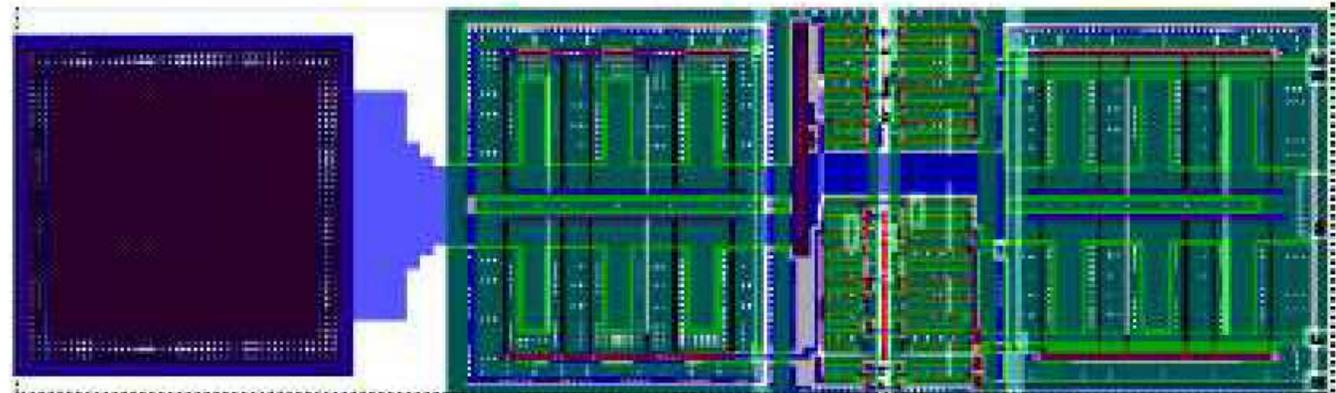
Bonding Pad



Where have you seen this before?



I/O Pad Drivers, revisited



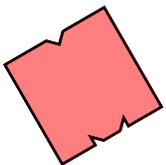
←→
60–80μm

ESD
diodes

I/O
buffers

ESD
diodes

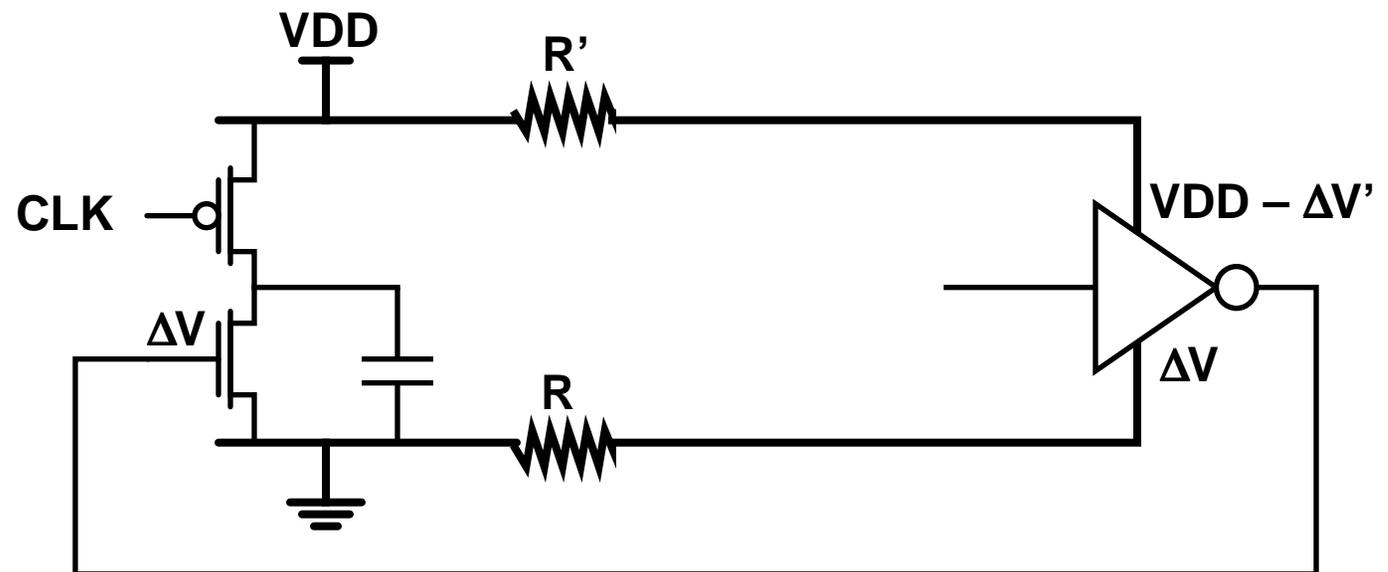
Oh yeah ...



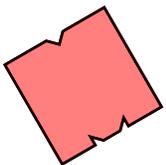
Resistive Parasitics

Basic Idea: IR drops over long distances

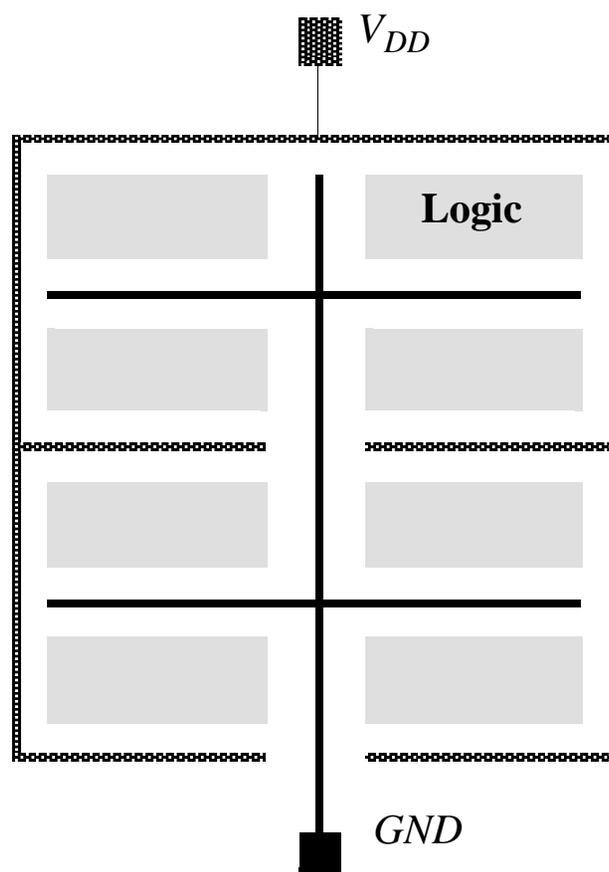
Power Rails



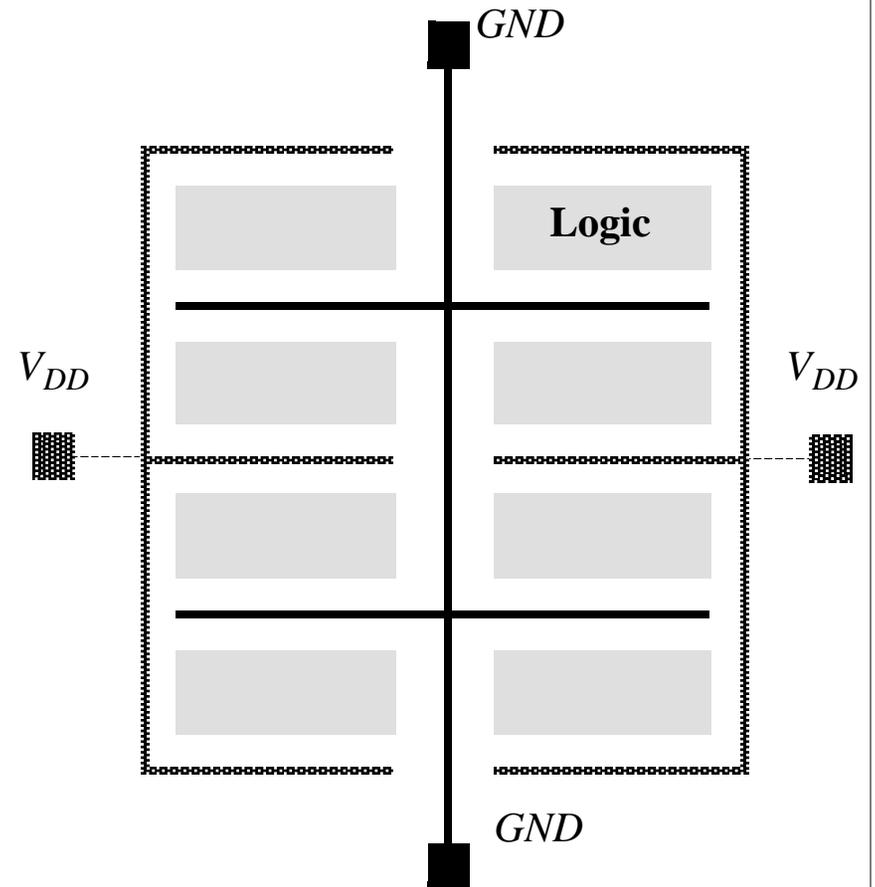
Possible to get relatively large non-zero voltage at input: reduces noise margins



Power/Ground Distribution



(a) Finger-shaped network



(b) Network with multiple supply pins



Resistive Parasitics

IR Drops and RC Delay over long wires

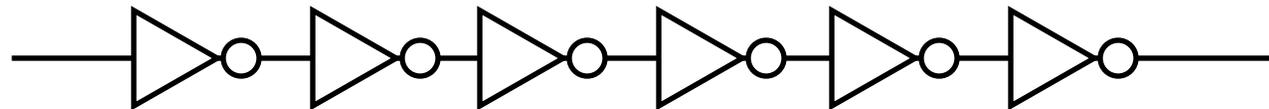
- (remember: delay of wire is quadratic w/ its length)

Solution: repeaters or pipelining

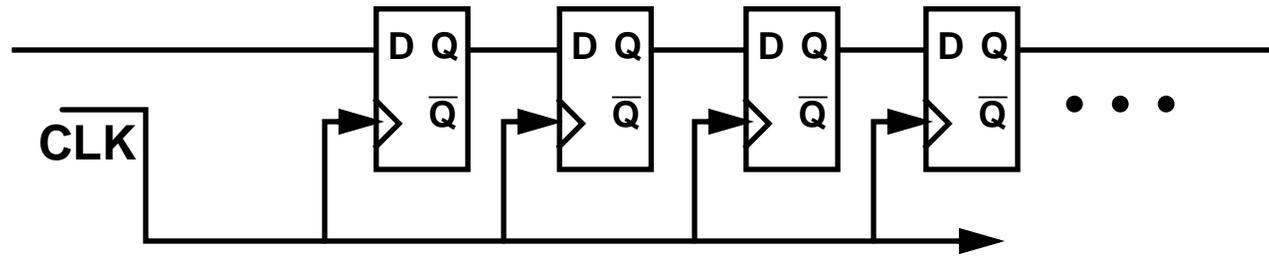
Instead of this:



Do this:

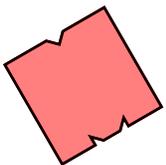
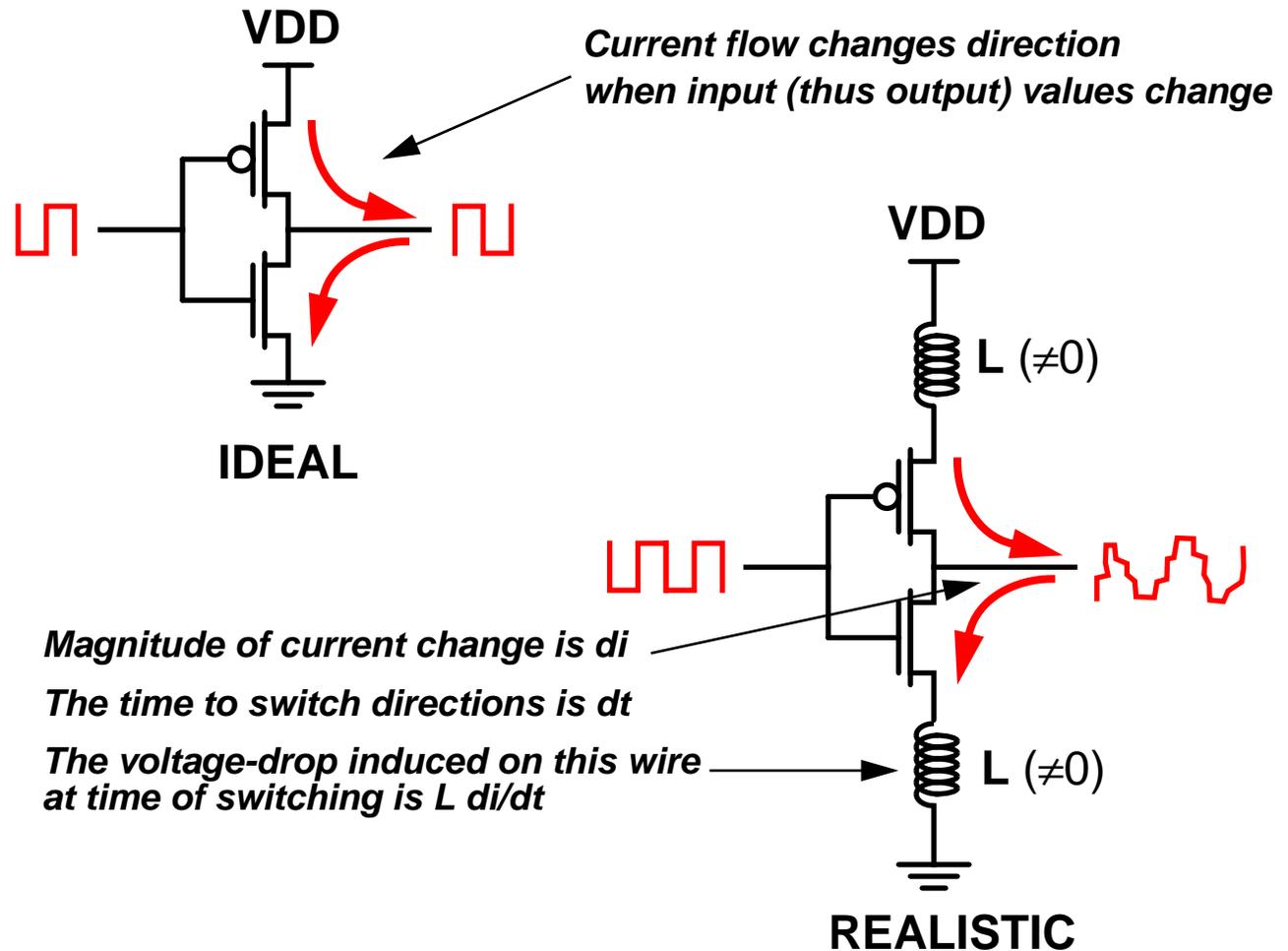


Or this:



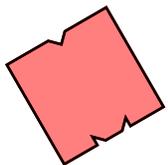
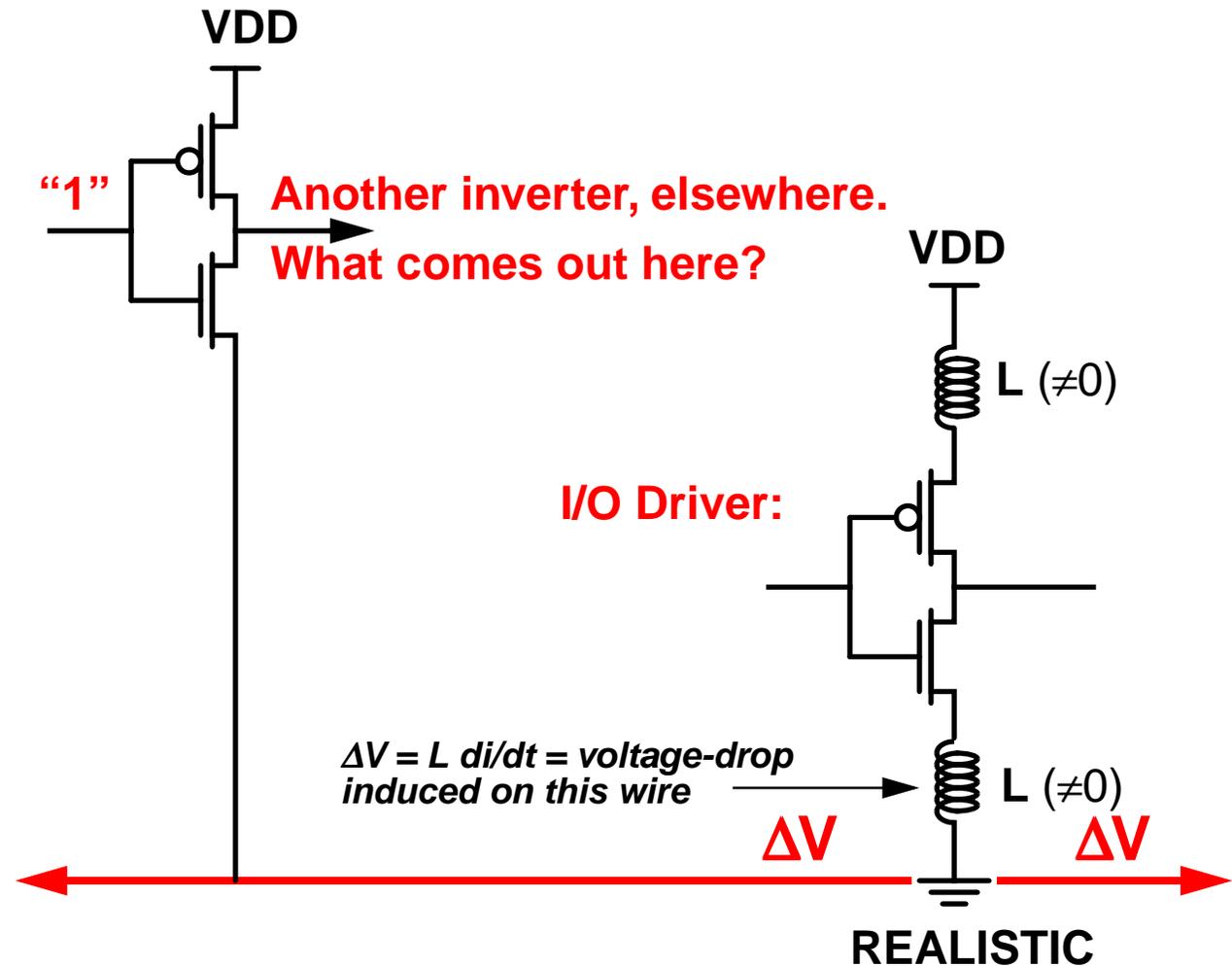
Inductive Parasitics

$L \, di/dt$ noise (ground bounce):



Inductive Parasitics

L di/dt noise (ground bounce):



Inductive Parasitics

Simultaneous Switching Noise:

